

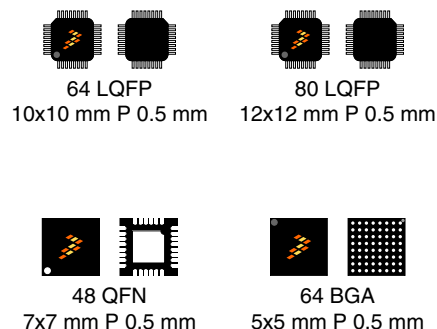
# Kinetis KL33 Microcontroller

48 MHz ARM® Cortex®-M0+ and 64 KB Flash

The KL33 series is optimized for cost-sensitive and battery-powered applications requiring low-power segment LCD. The product offers:

- Low power segment LCD up to 40x8/42x6/44x4
- Embedded ROM with boot loader for flexible program upgrade
- High accuracy internal voltage and clock reference
- FlexIO to support any standard and customized serial peripheral emulation
- Hardware CRC module
- Down to 60uA/MHz in very low power run mode and 1.83uA in deep sleep mode (RAM + RTC retained)

**MKL33Z32Vxx4**  
**MKL33Z64Vxx4**



## Core Processor

- ARM® Cortex®-M0+ core up to 48 MHz

## Memories

- 32/64 KB program flash memory
- 4/8 KB SRAM
- 8 KB ROM with build-in bootloader
- 32-byte backup register

## System

- 4-channel asynchronous DMA controller
- Watchdog
- Low-leakage wakeup unit
- Two-pin Serial Wire Debug (SWD) programming and debug interface
- Micro Trace Buffer
- Bit manipulation engine
- Interrupt controller

## Clocks

- 48 MHz high accuracy (up to 0.5%) internal reference clock
- 8MHz/2MHz high accuracy (up to 3%) internal reference clock
- 1KHz reference clock active under all low-power modes (except VLLS0)
- 32–40KHz and 3–32MHz crystal oscillator

## Peripherals

- Segment LCD supporting up to 40x8/42x6/44x4 segments
- One UART module supporting ISO7816, operating up to 1.5 Mbit/s
- Two low-power UART modules supporting asynchronous operation in low-power modes
- Two I2C modules and I2C0 supporting up to 1 Mbit/s
- Two 16-bit SPI modules supporting up to 24 Mbit/s
- One FlexIO module supporting emulation of additional UART, IrDA, SPI, I2C, PWM and other serial modules, etc.
- One 16-bit 818 kbps ADC module with high accuracy internal voltage reference (Vref) and up to 20 channels
- High-speed analog comparator containing a 6-bit DAC for programmable reference input
- One 12-bit DAC
- 1.2 V internal voltage reference

## Timers

- One 6-channel Timer/PWM module
- Two 2-channel Timer/PWM modules
- One low-power timer
- Periodic interrupt timer
- Real time clock

## Operating Characteristics

- Voltage range: 1.71 to 3.6 V
- Flash write voltage range: 1.71 to 3.6 V
- Temperature range: –40 to 105 °C

## Packages

- 80 LQFP 12mm x 12mm, 0.5mm pitch, 1.6mm thickness
- 64 LQFP 10mm x 10mm, 0.5mm pitch, 1.6mm thickness
- 64 MAPBGA 5mm x 5mm, 0.5mm pitch, 1.23mm thickness (Package Your Way)
- 48 QFN 7mm x 7mm, 0.5mm pitch, 0.65mm thickness (Package Your Way)

## Security and Integrity

- 80-bit unique identification number per chip
- Advanced flash security
- Hardware CRC module

## I/O

- Up to 70 general-purpose input/output pins (GPIO) and 4 high-drive pad

## Low Power

- Down to 60uA/MHz in very low power run mode
- Down to 1.83uA in VLLS3 mode (RAM + RTC retained)
- Six flexible static modes

## Ordering Information

Product		Memory		Package		IO and ADC channel		
Part number	Marking (Line1/ Line2)	Flash (KB)	SRAM (KB)	Pin count	Package	GPIOs	GPIOs (INT/HD) <sup>1</sup>	ADC channels (SE/DP)
MKL33Z32VFT4	TBD	32	4	48	QFN	40	40/4	17/3
MKL33Z64VFT4	TBD	64	8	48	QFN	40	40/4	17/3
MKL33Z32VLH4	MKL33Z32/VLH4	32	4	64	LQFP	54	54/4	20/4
MKL33Z64VLH4	MKL33Z64/VLH4	64	8	64	LQFP	54	54/4	20/4
MKL33Z32VMP4	TBD	32	4	64	MAPBGA	54	54/4	20/4
MKL33Z64VMP4	TBD	64	8	64	MAPBGA	54	54/4	20/4
MKL33Z32VLK4	MKL33Z32VLK4	32	4	80	LQFP	70	70/4	20/4
MKL33Z64VLK4	MKL33Z64VLK4	64	8	80	LQFP	70	70/4	20/4

1. INT: interrupt pin numbers; HD: high drive pin numbers

## NOTE

The 48 QFN and 64 MAPBGA packages supporting MKLx3ZxxVFT4 and MKLx3ZxxVMP4 part numbers for this product are not yet available. However, these packages are included in Package Your Way program for Kinetis MCUs. Visit [freescale.com/KPYW](http://freescale.com/KPYW) for more details.

## Related Resources

Type	Description	Resource
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	<a href="#">Solution Advisor</a>
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.	KL3xPB <sup>1</sup>
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KL33P80M48SF3RM <sup>1</sup>
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	This document.

Table continues on the next page...

### Related Resources (continued)

Type	Description	Resource
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	KINETIS_L_0N01P <sup>1</sup>
Package drawing	Package dimensions are provided in package drawings.	<ul style="list-style-type: none"><li>• 64-LQFP: 98ASS23234W<sup>1</sup></li><li>• 64 MAPBGA: 98ASA00420D<sup>1</sup></li><li>• 48 QFN: 98ASA00616D<sup>1</sup></li><li>• 80 LQFP: 98ASS23174W<sup>1</sup></li></ul>

1. To find the associated resource, go to <http://www.freescale.com> and perform a search using this term.

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# 1 Ratings

## 1.1 Thermal handling ratings

**Table 1. Thermal handling ratings**

Symbol	Description	Min.	Max.	Unit	Notes
T <sub>STG</sub>	Storage temperature	–55	150	°C	1
T <sub>SDR</sub>	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

## 1.2 Moisture handling ratings

**Table 2. Moisture handling ratings**

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

## 1.3 ESD handling ratings

**Table 3. ESD handling ratings**

Symbol	Description	Min.	Max.	Unit	Notes
V <sub>HBM</sub>	Electrostatic discharge voltage, human body model	–2000	+2000	V	1
V <sub>CDM</sub>	Electrostatic discharge voltage, charged-device model	–500	+500	V	2
I <sub>LAT</sub>	Latch-up current at ambient temperature of 105 °C	–100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

## 1.4 Voltage and current operating ratings

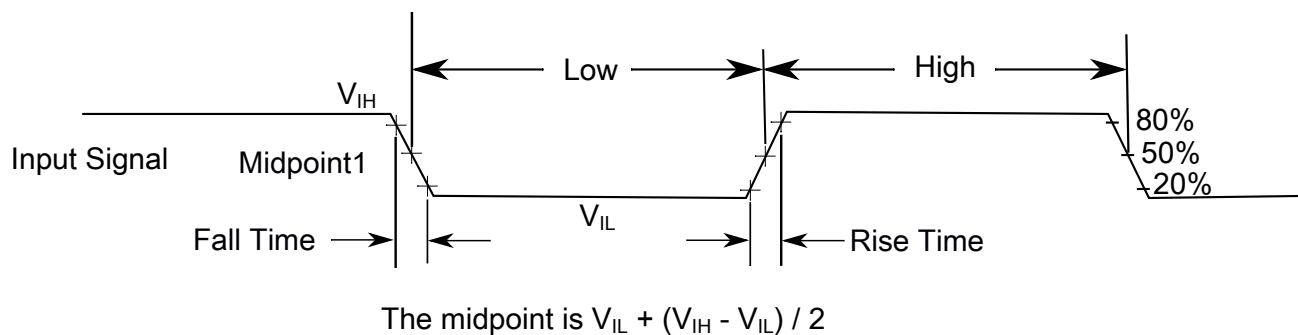
**Table 4. Voltage and current operating ratings**

Symbol	Description	Min.	Max.	Unit
$V_{DD}$	Digital supply voltage	-0.3	3.8	V
$I_{DD}$	Digital supply current	—	120	mA
$V_{IO}$	IO pin input voltage	-0.3	$V_{DD} + 0.3$	V
$I_D$	Instantaneous maximum current single pin limit (applies to all port pins)	-25	25	mA
$V_{DDA}$	Analog supply voltage	$V_{DD} - 0.3$	$V_{DD} + 0.3$	V

## 2 General

### 2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



**Figure 1. Input signal measurement reference**

All digital I/O switching characteristics, unless otherwise specified, assume that the output pins have the following characteristics.

- $C_L = 30$  pF loads
- Slew rate disabled
- Normal drive strength

### 2.2 Nonswitching electrical specifications

## 2.2.1 Voltage and current operating requirements

**Table 5. Voltage and current operating requirements**

Symbol	Description	Min.	Max.	Unit	Notes
$V_{DD}$	Supply voltage	1.71	3.6	V	
$V_{DDA}$	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	$V_{DD}$ -to- $V_{DDA}$ differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	$V_{SS}$ -to- $V_{SSA}$ differential voltage	-0.1	0.1	V	
$V_{IH}$	Input high voltage <ul style="list-style-type: none"> <li><math>2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}</math></li> <li><math>1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}</math></li> </ul>	$0.7 \times V_{DD}$	—	V	
		$0.75 \times V_{DD}$	—	V	
$V_{IL}$	Input low voltage <ul style="list-style-type: none"> <li><math>2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}</math></li> <li><math>1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}</math></li> </ul>	—	$0.35 \times V_{DD}$	V	
		—	$0.3 \times V_{DD}$	V	
$V_{HYS}$	Input hysteresis	$0.06 \times V_{DD}$	—	V	
$I_{ICIO}$	IO pin negative DC injection current — single pin <ul style="list-style-type: none"> <li><math>V_{IN} &lt; V_{SS}-0.3\text{V}</math></li> </ul>	-3	—	mA	1
$I_{ICcont}$	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pins <ul style="list-style-type: none"> <li>Negative current injection</li> </ul>	-25	—	mA	
$V_{ODPU}$	Open drain pullup voltage level	$V_{DD}$	$V_{DD}$	V	2
$V_{SRAM}$	$V_{DD}$ voltage required to retain SRAM	1.2	—	V	

1. All I/O pins are internally clamped to  $V_{SS}$  through a ESD protection diode. There is no diode connection to  $V_{DD}$ . If  $V_{IN}$  greater than  $V_{IO\_MIN}$  ( $= V_{SS}-0.3\text{ V}$ ) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as  $R = (V_{IO\_MIN} - V_{IN})/|I_{ICIO}|$ .
2. Open drain outputs must be pulled to  $V_{DD}$ .

## 2.2.2 LVD and POR operating requirements

**Table 6.  $V_{DD}$  supply LVD and POR operating requirements**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$V_{POR}$	Falling $V_{DD}$ POR detect voltage	0.8	1.1	1.5	V	—
$V_{LVDH}$	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	—
	Low-voltage warning thresholds — high range					1

Table continues on the next page...

**Table 6.  $V_{DD}$  supply LVD and POR operating requirements (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$V_{LVW1H}$	• Level 1 falling (LVWV = 00)	2.62	2.70	2.78	V	
$V_{LVW2H}$	• Level 2 falling (LVWV = 01)	2.72	2.80	2.88	V	
$V_{LVW3H}$	• Level 3 falling (LVWV = 10)	2.82	2.90	2.98	V	
$V_{LVW4H}$	• Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	
$V_{HYSH}$	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	—
$V_{LVDL}$	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	—
$V_{LVW1L}$	Low-voltage warning thresholds — low range • Level 1 falling (LVWV = 00)	1.74	1.80	1.86	V	1
$V_{LVW2L}$	• Level 2 falling (LVWV = 01)	1.84	1.90	1.96	V	
$V_{LVW3L}$	• Level 3 falling (LVWV = 10)	1.94	2.00	2.06	V	
$V_{LVW4L}$	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	V	
$V_{HYSL}$	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	—
$V_{BG}$	Bandgap voltage reference	0.97	1.00	1.03	V	—
$t_{LPO}$	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	—

1. Rising thresholds are falling threshold + hysteresis voltage

## 2.2.3 Voltage and current operating behaviors

**Table 7. Voltage and current operating behaviors**

Symbol	Description	Min.	Max.	Unit	Notes
$V_{OH}$	Output high voltage — normal drive pad • $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ , $I_{OH} = -5\text{ mA}$	$V_{DD} - 0.5$	—	V	1
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$ , $I_{OH} = -1.5\text{ mA}$	$V_{DD} - 0.5$	—	V	
$V_{OH}$	Output high voltage — high drive pad • $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ , $I_{OH} = -18\text{ mA}$	$V_{DD} - 0.5$	—	V	1
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$ , $I_{OH} = -6\text{ mA}$	$V_{DD} - 0.5$	—	V	
$I_{OHT}$	Output high current total for all ports	—	100	mA	
$V_{OL}$	Output low voltage — normal drive pad • $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ , $I_{OL} = 5\text{ mA}$	—	0.5	V	1
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$ , $I_{OL} = 1.5\text{ mA}$	—	0.5	V	
$V_{OL}$	Output low voltage — high drive pad				1

Table continues on the next page...



**Table 7. Voltage and current operating behaviors (continued)**

Symbol	Description	Min.	Max.	Unit	Notes
	<ul style="list-style-type: none"> <li>• <math>2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}</math>, <math>I_{OL} = 18\text{ mA}</math></li> <li>• <math>1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}</math>, <math>I_{OL} = 6\text{ mA}</math></li> </ul>	—	0.5	V	
		—	0.5	V	
$I_{OLT}$	Output low current total for all ports	—	100	mA	
$I_{IN}$	Input leakage current (per pin) for full temperature range	—	1	$\mu\text{A}$	2
$I_{IN}$	Input leakage current (per pin) at 25 °C	—	0.025	$\mu\text{A}$	2
$I_{IN}$	Input leakage current (total all pins) for full temperature range	—	80	$\mu\text{A}$	2
$I_{OZ}$	Hi-Z (off-state) leakage current (per pin)	—	1	$\mu\text{A}$	
$R_{PU}$	Internal pullup resistors	20	50	k $\Omega$	3

1. PTB0, PTB1, PTC3, and PTD7 I/O have both high drive and normal drive capability selected by the associated PORTx\_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. Measured at  $V_{DD} = 3.6\text{ V}$
3. Measured at  $V_{DD}$  supply voltage =  $V_{DD}$  min and  $V_{input} = V_{SS}$

## 2.2.4 Power mode transition operating behaviors

All specifications except  $t_{POR}$  and  $VLLSx \rightarrow \text{RUN}$  recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- HIRC clock mode

**Table 8. Power mode transition operating behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{POR}$	After a POR event, amount of time from the point $V_{DD}$ reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	$\mu\text{s}$	1
	• $VLLS0 \rightarrow \text{RUN}$	—	152	166	$\mu\text{s}$	
	• $VLLS1 \rightarrow \text{RUN}$	—	152	166	$\mu\text{s}$	
	• $VLLS3 \rightarrow \text{RUN}$	—	93	104	$\mu\text{s}$	
	• $LLS \rightarrow \text{RUN}$	—	7.5	8	$\mu\text{s}$	

Table continues on the next page...

**Table 8. Power mode transition operating behaviors (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• VLPS → RUN	—	7.5	8	μs	
	• STOP → RUN	—	7.5	8	μs	

1. Normal boot (FTFA\_FOPT[LPBOOT]=11)

## 2.2.5 Power consumption operating behaviors

The maximum values stated in the following table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

### NOTE

The while (1) test is executed with flash cache enabled.

**Table 9. Power consumption operating behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I <sub>DDA</sub>	Analog supply current	—	—	See note	mA	1
I <sub>DD_RUNCO</sub>	Running CoreMark in flash in compute operation mode—48M HIRC mode, 48 MHz core / 24 MHz flash, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> <li>at 105 °C</li> </ul>	— —	4.74 4.9	4.93 5.10	mA	2
I <sub>DD_RUNCO</sub>	Running While(1) loop in flash in compute operation mode—48M HIRC mode, 48 MHz core / 24 MHz flash, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> <li>at 105 °C</li> </ul>	— —	3.27 3.42	3.43 3.59	mA	
I <sub>DD_RUN</sub>	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock disable 48 MHz core/24 MHz flash, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> <li>at 105 °C</li> </ul>	— —	5.63 5.79	5.86 6.02	mA	2
I <sub>DD_RUN</sub>	Run mode current—48M HIRC mode, running CoreMark in flash all peripheral clock disable, 24 MHz core/12 MHz flash, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> <li>at 105 °C</li> </ul>	— —	3.47 3.63	3.61 3.78	mA	2,

Table continues on the next page...

**Table 9. Power consumption operating behaviors (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$I_{DD\_RUN}$	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock disable 12 MHz core/6 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C • at 105 °C	— —	2.37 2.53	2.56 2.73	mA	2
$I_{DD\_RUN}$	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock enable 48 MHz core/24 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C • at 105 °C	— —	6.91 7.07	7.19 7.35	mA	2
$I_{DD\_RUN}$	Run mode current—48M HIRC mode, running While(1) loop in flash all peripheral clock disable, 48 MHz core/24 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C • at 105 °C	— —	4.14 4.3	4.31 4.47	mA	
$I_{DD\_RUN}$	Run mode current—48M HIRC mode, running While(1) loop in Flash all peripheral clock disable, 24 MHz core/12 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C • at 105 °C	— —	2.7 2.86	2.92 3.09	mA	
$I_{DD\_RUN}$	Run mode current—48M HIRC mode, Running While(1) loop in Flash all peripheral clock disable, 12 MHz core/6 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C • at 105 °C	— —	1.99 2.14	2.15 2.31	mA	
$I_{DD\_RUN}$	Run mode current—48M HIRC mode, Running While(1) loop in Flash all peripheral clock enable, 48 MHz core/24 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C • at 105 °C	— —	5.39 5.56	5.61 5.78	mA	
$I_{DD\_VLPRCO}$	Very Low Power Run Core Mark in Flash in Compute Operation mode: Core@4MHz, Flash @1MHz, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	739	827.68	$\mu\text{A}$	
$I_{DD\_VLPRCO}$	Very-low-power-run While(1) loop in SRAM in compute operation mode— 8 MHz LIRC mode, 4 MHz core / 1 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	339	406.8	$\mu\text{A}$	
$I_{DD\_VLPRCO}$	Very-low-power run While(1) loop in SRAM in compute operation mode:—2 MHz LIRC mode, 2 MHz core / 0.5 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	152	197.6	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral					

Table continues on the next page...

**Table 9. Power consumption operating behaviors (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	clock disable, 2 MHz core / 0.5 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	119	178.5	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 125 kHz core / 31.25 kHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	41	89.39	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 4 MHz core / 1 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	277	360.1	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in flash all peripheral clock enable, 4 MHz core / 1 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	343	425.32	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 4 MHz core / 1 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	375	450	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM all peripheral clock enable, 4 MHz core / 1 MHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	441	529.2	$\mu\text{A}$	
$I_{DD\_VLPR}$	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all peripheral clock disable, 125 kHz core / 31.25 kHz flash, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	45	103.5	$\mu\text{A}$	
$I_{DD\_WAIT}$	Wait mode current—core disabled, 48 MHz system/24 MHz bus, flash disabled (flash doze enabled), all peripheral clocks disabled, MCG_Lite under HIRC mode, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	2.14	2.50	mA	
$I_{DD\_WAIT}$	Wait mode current—core disabled, 24 MHz system/12 MHz bus, flash disabled (flash doze enabled), all peripheral clocks disabled, MCG_Lite under HIRC mode, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	1.41	1.62	mA	
$I_{DD\_VLPW}$	Very-low-power wait mode current, core disabled, 4 MHz system/ 1 MHz bus and flash, all peripheral clocks disabled, $V_{DD} = 3.0\text{ V}$ • at 25 °C	—	193	239.023	$\mu\text{A}$	

Table continues on the next page...

**Table 9. Power consumption operating behaviors (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I <sub>DD_VLPW</sub>	Very-low-power wait mode current, core disabled, 2 MHz system/ 0.5 MHz bus and flash, all peripheral clocks disabled, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> </ul>	—	78	124.8	μA	
I <sub>DD_VLPW</sub>	Very-low-power wait mode current, core disabled, 125 kHz system/ 31.25 kHz bus and flash, all peripheral clocks disabled, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> </ul>	—	39	78	μA	
I <sub>DD_PSTOP2</sub>	Partial Stop 2, core and system clock disabled, 12 MHz bus and flash, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> </ul>	—	1.72	2.06	mA	
I <sub>DD_PSTOP2</sub>	Partial Stop 2, core and system clock disabled, flash doze enabled, 12 MHz bus, V <sub>DD</sub> = 3.0 V <ul style="list-style-type: none"> <li>at 25 °C</li> </ul>	—	1.1	1.32	mA	
I <sub>DD_STOP</sub>	Stop mode current at 3.0 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50 °C</li> <li>at 85 °C</li> <li>at 105 °C</li> </ul>	—	161	178.2	μA	
		—	171.9	181.17		
		—	206.8	229.72		
		—	255.9	302.01		
I <sub>DD_VLPS</sub>	Very-low-power stop mode current at 3.0 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50 °C</li> <li>at 85 °C</li> <li>at 105 °C</li> </ul>	—	2.20	3.80	μA	
		—	4.57	8.03		
		—	18.02	31.98		
		—	39.60	65.80		
I <sub>DD_VLPS</sub>	Very-low-power stop mode current at 1.8 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50 °C</li> <li>at 85 °C</li> <li>at 105 °C</li> </ul>	—	2.13	3.80	μA	
		—	4.42	7.94		
		—	17.53	31.58		
		—	38.55	65.18		
I <sub>DD_LLS</sub>	Low-leakage stop mode current, all peripheral disable, at 3.0 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50 °C</li> <li>at 70 °C</li> <li>at 85 °C</li> <li>at 105 °C</li> </ul>	—	1.63	2.25	μA	
		—	2.42	3.55		
		—	4.22	7.08		
		—	7.16	10.22		
		—	15.34	22.69		
I <sub>DD_LLS</sub>	Low-leakage stop mode current with RTC current, at 3.0 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> </ul>	—	2.3	2.99	μA	

Table continues on the next page...

**Table 9. Power consumption operating behaviors (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> <li>• at 50 °C</li> <li>• at 70 °C</li> <li>• at 85 °C</li> <li>• at 105 °C</li> </ul>	—	3.12	4.50		
		—	4.96	7.71		
		—	7.93	10.75		
		—	16.02	22.99		
I <sub>DD_LLS</sub>	Low-leakage stop mode current with RTC current, at 1.8 V <ul style="list-style-type: none"> <li>• at 25 °C and below</li> <li>• at 50 °C</li> <li>• at 70 °C</li> <li>• at 85 °C</li> <li>• at 105 °C</li> </ul>	—	2.03	2.55	μA	3
		—	2.81	3.95		
		—	4.53	7.30		
		—	7.31	10.25		
		—	14.93	22.72		
I <sub>DD_VLLS3</sub>	Very-low-leakage stop mode 3 current, all peripheral disable, at 3.0 V <ul style="list-style-type: none"> <li>• at 25 °C and below</li> <li>• at 50 °C</li> <li>• at 70 °C</li> <li>• at 85 °C</li> <li>• at 105 °C</li> </ul>	—	1.16	1.65	μA	
		—	1.72	2.65		
		—	3.04	5.70		
		—	5.21	7.79		
		—	11.33	17.63		
I <sub>DD_VLLS3</sub>	Very-low-leakage stop mode 3 current with RTC current, at 3.0 V <ul style="list-style-type: none"> <li>• at 25 °C and below</li> <li>• at 50 °C</li> <li>• at 70 °C</li> <li>• at 85 °C</li> <li>• at 105 °C</li> </ul>	—	1.83	2.35	μA	3
		—	2.43	3.39		
		—	3.78	5.95		
		—	5.98	8.14		
		—	12.02	17.89		
I <sub>DD_VLLS3</sub>	Very-low-leakage stop mode 3 current with RTC current, at 1.8 V <ul style="list-style-type: none"> <li>• at 25 °C and below</li> <li>• at 50 °C</li> <li>• at 70 °C</li> <li>• at 85 °C</li> <li>• at 105 °C</li> </ul>	—	1.58	1.98	μA	3
		—	2.13	3.17		
		—	3.37	5.80		
		—	5.4	7.83		
		—	10.99	16.86		
I <sub>DD_VLLS1</sub>	Very-low-leakage stop mode 1 current all peripheral disabled at 3.0 V <ul style="list-style-type: none"> <li>• at 25 °C and below</li> <li>• at 50 °C</li> <li>• at 70 °C</li> </ul>	—	0.62	1.06		
		—	0.99	1.43		
		—	1.88	2.65	μA	
		—	3.41	4.53		

Table continues on the next page...

**Table 9. Power consumption operating behaviors (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> <li>at 85°C</li> <li>at 105 °C</li> </ul>	—	7.89	9.99		
I <sub>DD_VLLS1</sub>	Very-low-leakage stop mode 1 current RTC enabled at 3.0 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50°C</li> <li>at 70°C</li> <li>at 85°C</li> <li>at 105 °C</li> </ul>	—	1.31	1.52	μA	3
		—	1.7	2.04		
		—	2.6	3.20		
		—	4.14	4.69		
		—	8.51	10.46		
I <sub>DD_VLLS1</sub>	Very-low-leakage stop mode 1 current RTC enabled at 1.8 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50°C</li> <li>at 70°C</li> <li>at 85°C</li> <li>at 105 °C</li> </ul>	—	1.06	1.35	μA	3
		—	1.39	1.73		
		—	2.18	2.83		
		—	3.54	4.60		
		—	7.43	9.97		
I <sub>DD_VLLS0</sub>	Very-low-leakage stop mode 0 current all peripheral disabled (SMC_STOPCTRL[PORPO] = 0) at 3.0 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50 °C</li> <li>at 70 °C</li> <li>at 85 °C</li> <li>at 105 °C</li> </ul>	—	278	385	nA	
		—	578	1013		
		—	1530	2015		
		—	3070	3617		
		—	7550	9900		
I <sub>DD_VLLS0</sub>	Very-low-leakage stop mode 0 current all peripheral disabled (SMC_STOPCTRL[PORPO] = 1) at 3 V <ul style="list-style-type: none"> <li>at 25 °C and below</li> <li>at 50 °C</li> <li>at 70 °C</li> <li>at 85 °C</li> <li>at 105 °C</li> </ul>	—	95	218	nA	
		—	412	653		
		—	1350	1683		
		—	2900	3428		
		—	7380	9785		

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. MCG\_Lite configured for HIRC mode. CoreMark benchmark compiled using IAR 7.20 with optimization level high, optimized for balanced.
3. RTC uses external 32 kHz crystal as clock source, and the current includes ERCLK32K power consumption.

**Table 10. Low power mode peripheral adders — typical value**

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I <sub>IRC8MHz</sub>	8 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 8 MHz IRC enabled, MCG_SC[FCRDIV]=000b, MCG_MC[LIRC_DIV2]=000b.	85	87	88	88	89	90	μA
I <sub>IRC2MHz</sub>	2 MHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 2 MHz IRC enabled, MCG_SC[FCRDIV]=000b, MCG_MC[LIRC_DIV2]=000b.	28	28	28	28	28	28	μA
I <sub>EREFSTEN4MHz</sub>	External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.	206	224	230	238	245	253	μA
I <sub>EREFSTEN32KHz</sub>	External 32 kHz crystal clock adder by means of setting the OSC0_CR[EREFSTEN and EREFSTEN] bits to 1 and SIM_SOPT1[OSC32KSEL] to 01. Measured by entering all modes with the crystal enabled. <ul style="list-style-type: none"> <li>• VLLS1</li> <li>• VLLS3</li> <li>• LLS</li> <li>• VLPS</li> <li>• STOP</li> </ul>	440	490	540	560	570	580	nA
		440	490	540	560	570	580	
		490	490	540	560	570	680	
		510	560	560	560	610	680	
		510	560	560	560	610	680	
I <sub>LPTMR</sub>	LPTMR peripheral adder measured by placing the device in VLLS1 mode with LPTMR enabled using LPO.	30	30	30	85	100	200	nA
I <sub>CMP</sub>	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	16	16	16	16	16	16	μA
I <sub>RTC</sub>	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	582	627	638	662	682	760	nA
I <sub>UART</sub>	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate.							

Table continues on the next page...



**Table 10. Low power mode peripheral adders — typical value (continued)**

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
	Includes selected clock source power consumption. <ul style="list-style-type: none"> <li>IRC8M (8 MHz internal reference clock)</li> <li>IRC2M (2 MHz internal reference clock)</li> </ul>	105 34	110 34	110 34	111 34	112 34	114 34	μA
I <sub>TPM</sub>	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents. <ul style="list-style-type: none"> <li>IRC8M (8 MHz internal reference clock)</li> <li>IRC2M (2 MHz internal reference clock)</li> </ul>	130 40	130 40	130 40	130 40	130 40	130 40	μA
I <sub>BG</sub>	Bandgap adder when BGEN bit is set and device is placed in VLPx or VLLSx mode.	45	45	45	45	45	45	μA
I <sub>ADC</sub>	ADC peripheral adder combining the measured values at V <sub>DD</sub> and V <sub>DDA</sub> by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	320	320	320	320	320	320	μA
I <sub>LCD</sub>	LCD peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the OSC0_CR[EREFSTEN, EREFSTEN] bits. VIREG disabled, resistor bias network enabled, 1/8 duty cycle, 8 x 36 configuration for driving 288 Segments, 32 Hz frame rate, no LCD glass connected. Includes ERCLK32K (32 kHz external crystal) power consumption.	4.9	4.9	4.9	4.9	4.9	4.9	μA

### 2.2.5.1 Diagram: Typical IDD\_RUN operating behavior

The following data was measured under these conditions:

- MCG-Lite in HIRC for run mode, and LIRC for VLPR mode
- No GPIOs toggled
- Code execution from flash
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

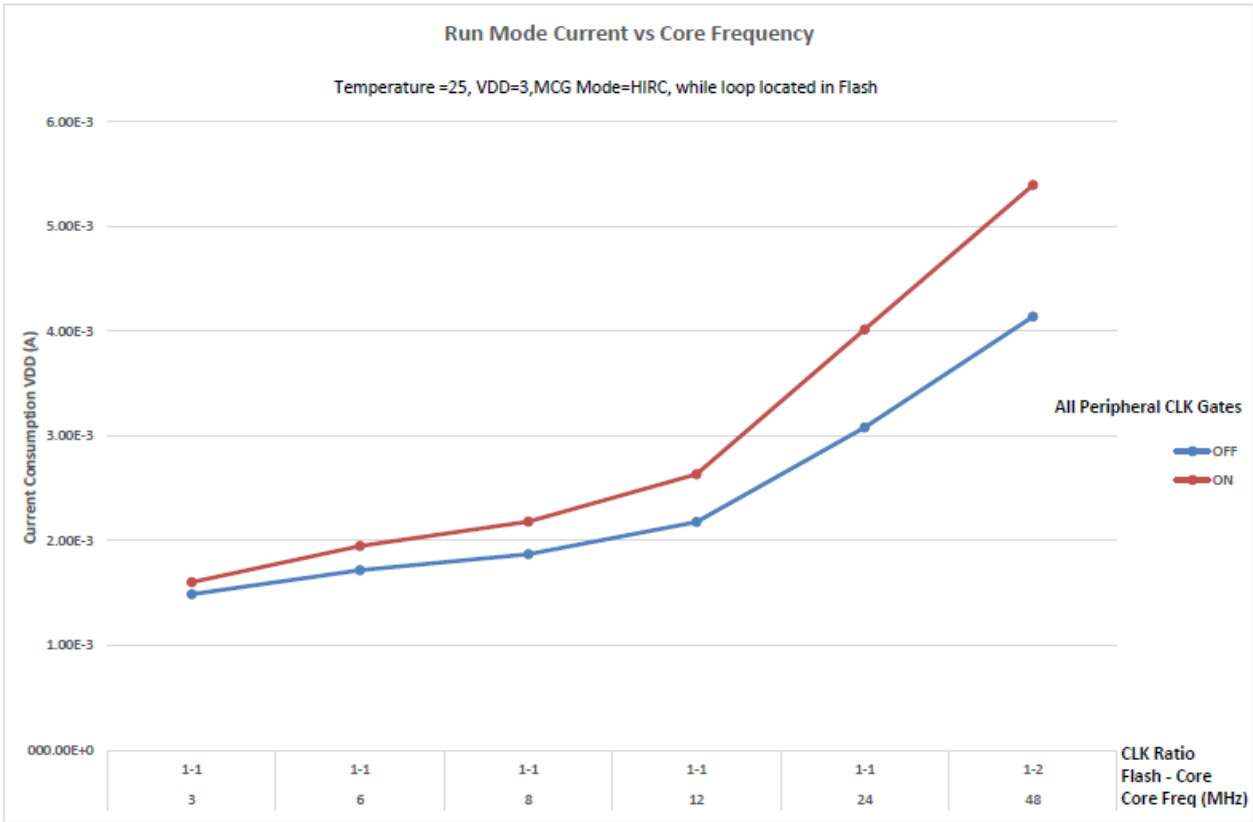
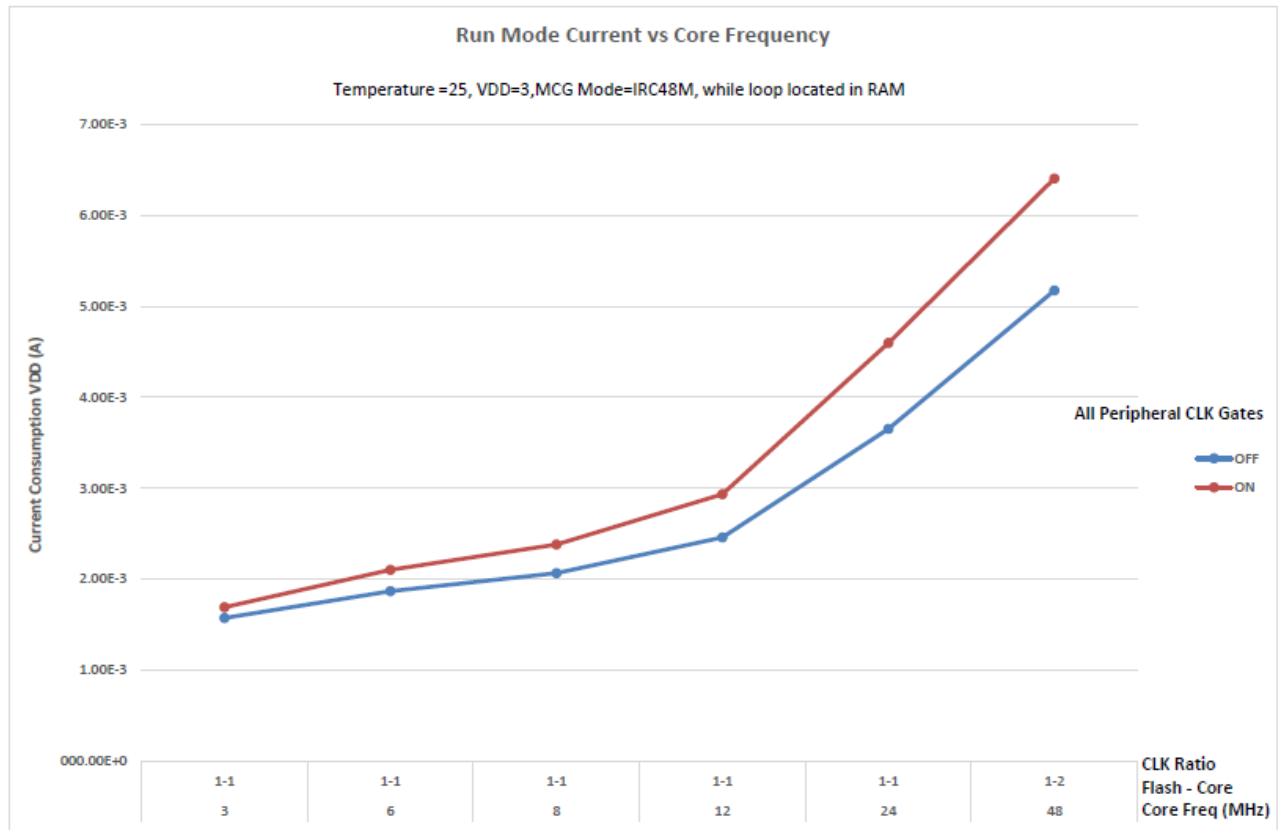
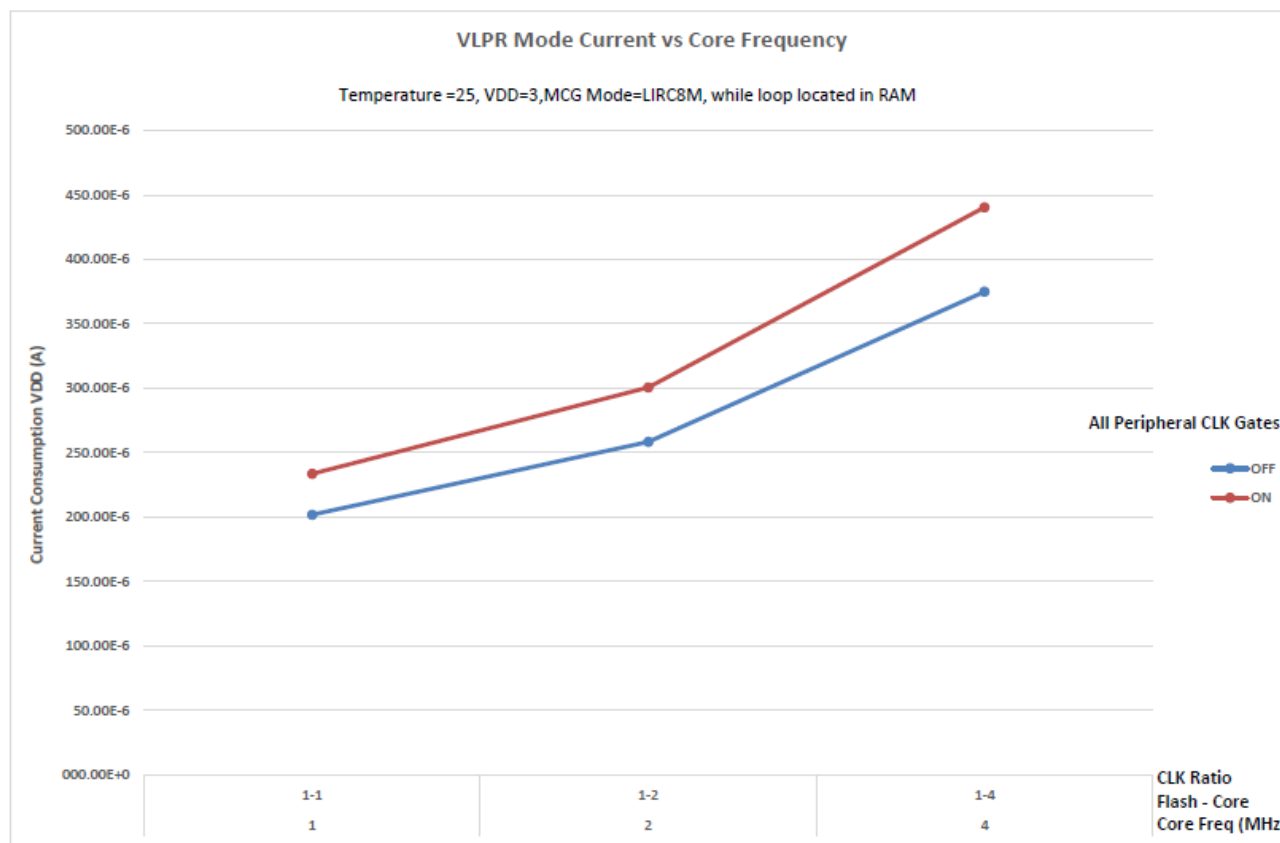


Figure 2. Run mode supply current vs. core frequency





**Figure 3. VLPR mode current vs. core frequency**

## 2.2.6 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components, and MCU software operation play a significant role in the EMC performance. The system designer can consult the following Freescale applications notes, available on [freescale.com](http://freescale.com) for advice and guidance specifically targeted at optimizing EMC performance.

- AN2321: Designing for Board Level Electromagnetic Compatibility
- AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers
- AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers
- AN2764: Improving the Transient Immunity Performance of Microcontroller-Based Applications

- AN1259: System Design and Layout Techniques for Noise Reduction in MCU-Based Systems
- KL-QRUG (Kinetis L-series Quick Reference).

## 2.2.7 Capacitance attributes

Table 11. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C <sub>IN</sub>	Input capacitance	—	7	pF

## 2.3 Switching specifications

### 2.3.1 Device clock specifications

Table 12. Device clock specifications

Symbol	Description	Min.	Max.	Unit
Normal run mode				
f <sub>SYS</sub>	System and core clock	—	48	MHz
f <sub>BUS</sub>	Bus clock	—	24	MHz
f <sub>FLASH</sub>	Flash clock	—	24	MHz
f <sub>LPTMR</sub>	LPTMR clock	—	24	MHz
VLPR and VLPS modes <sup>1</sup>				
f <sub>SYS</sub>	System and core clock	—	4	MHz
f <sub>BUS</sub>	Bus clock	—	1	MHz
f <sub>FLASH</sub>	Flash clock	—	1	MHz
f <sub>LPTMR</sub>	LPTMR clock <sup>2</sup>	—	24	MHz
f <sub>LPTMR_ERCLK</sub>	LPTMR external reference clock	—	16	MHz
f <sub>osc_hi_2</sub>	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	—	16	MHz
f <sub>TPM</sub>	TPM asynchronous clock	—	8	MHz
f <sub>LPUART0/1</sub>	LPUART0/1 asynchronous clock	—	8	MHz

1. The frequency limitations in VLPR and VLPS modes here override any frequency specification listed in the timing specification for any other module. These same frequency limits apply to VLPS, whether VLPS was entered from RUN or from VLPR.
2. The LPTMR can be clocked at this speed in VLPR or VLPS only when the source is an external pin.

## 2.3.2 General switching specifications

These general-purpose specifications apply to all signals configured for GPIO and UART signals.

**Table 13. General switching specifications**

Description	Min.	Max.	Unit	Notes
GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
Port rise and fall time	—	36	ns	3

1. The synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. 75 pF load

## 2.4 Thermal specifications

### 2.4.1 Thermal operating requirements

**Table 14. Thermal operating requirements**

Symbol	Description	Min.	Max.	Unit	Notes
T <sub>J</sub>	Die junction temperature	−40	125	°C	
T <sub>A</sub>	Ambient temperature	−40	105	°C	1

1. Maximum T<sub>A</sub> can be exceeded only if the user ensures that T<sub>J</sub> does not exceed the maximum. The simplest method to determine T<sub>J</sub> is:  $T_J = T_A + \theta_{JA} \times \text{chip power dissipation}$ .

### 2.4.2 Thermal attributes

#### NOTE

The 48 QFN and 64 MAPBGA packages for this product are not yet available. However, these packages are included in Package Your Way program for Kinetis MCUs. Visit [freescale.com/KPYW](http://freescale.com/KPYW) for more details.

**Table 15. Thermal attributes**

Board type	Symbol	Description	64 LQFP	80 LQFP	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	71	58	°C/W	1, 2
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	53	43	°C/W	1, 2
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	60	47	°C/W	1, 3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	46	37	°C/W	1, 3,
—	$R_{\theta JB}$	Thermal resistance, junction to board	35	26	°C/W	4
—	$R_{\theta JC}$	Thermal resistance, junction to case	21	15	°C/W	5
—	$\Psi_{JT}$	Thermal characterization parameter, junction to package top outside center (natural convection)	5	3	°C/W	6

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with natural convection for horizontally oriented board. Board meets JESD51-9 specification for 1s or 2s2p board, respectively.
3. Per JEDEC JESD51-6 with forced convection for horizontally oriented board. Board meets JESD51-9 specification for 1s or 2s2p board, respectively.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

## 3 Peripheral operating requirements and behaviors

### 3.1 Core modules

#### 3.1.1 SWD electricals

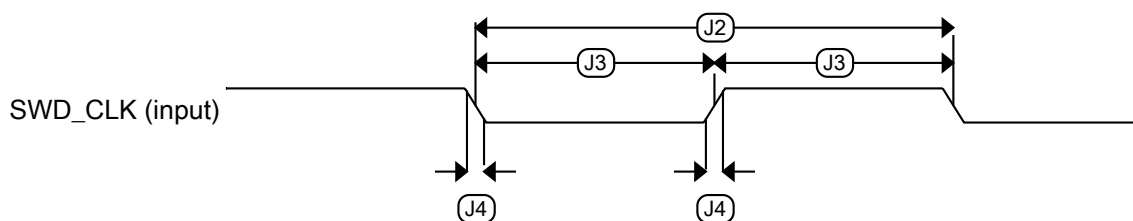
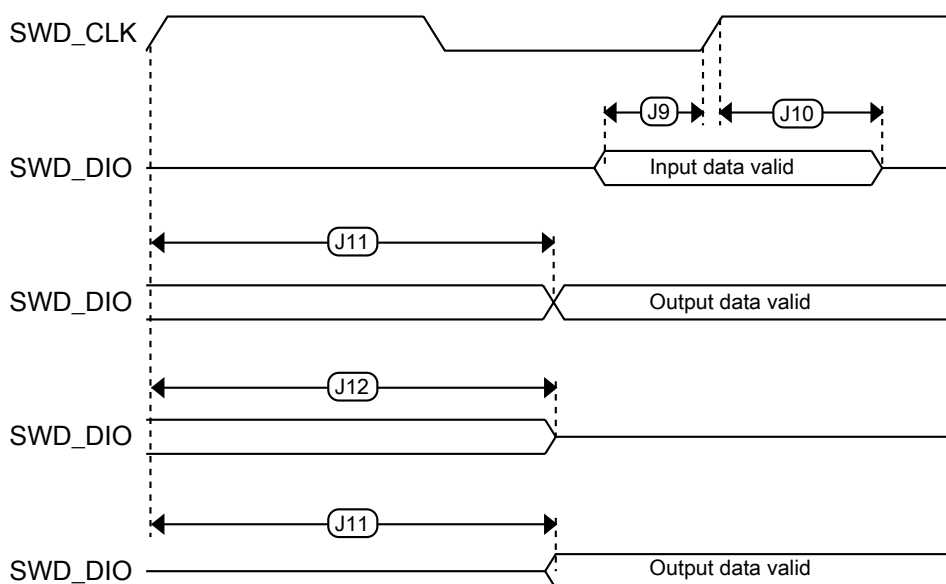
**Table 16. SWD full voltage range electricals**

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			

*Table continues on the next page...*

**Table 16. SWD full voltage range electricals (continued)**

Symbol	Description	Min.	Max.	Unit
	• Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width • Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

**Figure 4. Serial wire clock input timing****Figure 5. Serial wire data timing**



## 3.2 System modules

There are no specifications necessary for the device's system modules.

## 3.3 Clock modules

### 3.3.1 MCG-Lite specifications

**Table 17. IRC48M specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$I_{DD48M}$	Supply current	—	400	500	$\mu A$	
$f_{irc48m}$	Internal reference frequency	—	48	—	MHz	
$\Delta f_{irc48m\_ol\_lv}$	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over temperature	—	$\pm 0.5$	$\pm 1.5$	$\%f_{irc48m}$	
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over temperature	—	$\pm 0.5$	$\pm 1.0$	$\%f_{irc48m}$	
$J_{cyc\_irc48m}$	Period Jitter (RMS)	—	35	150	ps	
$t_{irc48mst}$	Startup time	—	2	3	$\mu s$	

**Table 18. IRC8M/2M specification**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$I_{DD\_2M}$	Supply current in 2 MHz mode	—	14	17	$\mu A$	—
$I_{DD\_8M}$	Supply current in 8 MHz mode	—	30	35	$\mu A$	—
$f_{IRC\_2M}$	Output frequency	—	2	—	MHz	—
$f_{IRC\_8M}$	Output frequency	—	8	—	MHz	—
$f_{IRC\_T\_2M}$	Output frequency range (trimmed)	—	—	$\pm 3$	$\%f_{IRC}$	—
$f_{IRC\_T\_8M}$	Output frequency range (trimmed)	—	—	$\pm 3$	$\%f_{IRC}$	—
$T_{su\_2M}$	Startup time	—	—	12.5	$\mu s$	—
$T_{su\_8M}$	Startup time	—	—	12.5	$\mu s$	—

### 3.3.2 Oscillator electrical specifications

### 3.3.2.1 Oscillator DC electrical specifications

**Table 19. Oscillator DC electrical specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$V_{DD}$	Supply voltage	1.71	—	3.6	V	
$I_{DDOSC}$	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	μA	
	• 8 MHz (RANGE=01)	—	300	—	μA	
	• 16 MHz	—	950	—	μA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
$I_{DDOSC}$	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μA	
	• 4 MHz	—	400	—	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
$C_x$	EXTAL load capacitance	—	—	—		2, 3
$C_y$	XTAL load capacitance	—	—	—		2, 3
$R_F$	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
$R_S$	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
$V_{pp}$ <sup>5</sup>	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	

Table continues on the next page...

**Table 19. Oscillator DC electrical specifications (continued)**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V <sub>DD</sub>	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V <sub>DD</sub>	—	V	

1. V<sub>DD</sub>=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C<sub>x</sub>,C<sub>y</sub> can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R<sub>F</sub> is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

### 3.3.2.2 Oscillator frequency specifications

**Table 20. Oscillator frequency specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f <sub>osc_lo</sub>	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
f <sub>osc_hi_1</sub>	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
f <sub>osc_hi_2</sub>	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f <sub>ec_extal</sub>	Input clock frequency (external clock mode)	—	—	48	MHz	
t <sub>dc_extal</sub>	Input clock duty cycle (external clock mode)	40	50	60	%	
t <sub>cst</sub>	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	1, 2
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Proper PC board layout procedures must be followed to achieve specifications.
2. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG\_S register being set.

## 3.4 Memories and memory interfaces

### 3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

#### 3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

**Table 21. NVM program/erase timing specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{hvp\text{gm}4}$	Longword Program high-voltage time	—	7.5	18	$\mu\text{s}$	—
$t_{h\text{ver}sscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{h\text{ver}all}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

#### 3.4.1.2 Flash timing specifications — commands

**Table 22. Flash command timing specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1\text{sec}1k}$	Read 1s Section execution time (flash sector)	—	—	60	$\mu\text{s}$	1
$t_{pgmchk}$	Program Check execution time	—	—	45	$\mu\text{s}$	1
$t_{rdsrc}$	Read Resource execution time	—	—	30	$\mu\text{s}$	1
$t_{pgm4}$	Program Longword execution time	—	65	145	$\mu\text{s}$	—
$t_{er\text{sscr}}$	Erase Flash Sector execution time	—	14	114	ms	2
$t_{rd1all}$	Read 1s All Blocks execution time	—	—	0.9	ms	1
$t_{rdonce}$	Read Once execution time	—	—	25	$\mu\text{s}$	1
$t_{pgmonce}$	Program Once execution time	—	65	—	$\mu\text{s}$	—
$t_{er\text{all}}$	Erase All Blocks execution time	—	70	575	ms	2
$t_{vfykey}$	Verify Backdoor Access Key execution time	—	—	30	$\mu\text{s}$	1
$t_{er\text{allu}}$	Erase All Blocks Unsecure execution time	—	70	575	ms	2

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

### 3.4.1.3 Flash high voltage current behaviors

Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I <sub>DD_PGM</sub>	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I <sub>DD_ERS</sub>	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

### 3.4.1.4 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
Program Flash						
t <sub>nvmretp10k</sub>	Data retention after up to 10 K cycles	5	50	—	years	—
t <sub>nvmretp1k</sub>	Data retention after up to 1 K cycles	20	100	—	years	—
n <sub>nvmcycp</sub>	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at  $-40\text{ °C} \leq T_j \leq 125\text{ °C}$ .

## 3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

## 3.6 Analog

### 3.6.1 ADC electrical specifications

Using differential inputs can achieve better system accuracy than using single-end inputs.

### 3.6.1.1 16-bit ADC operating conditions

Table 25. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. <sup>1</sup>	Max.	Unit	Notes
V <sub>DDA</sub>	Supply voltage	Absolute	1.71	—	3.6	V	—
ΔV <sub>DDA</sub>	Supply voltage	Delta to V <sub>DD</sub> (V <sub>DD</sub> – V <sub>DDA</sub> )	-100	0	+100	mV	2
ΔV <sub>SSA</sub>	Ground voltage	Delta to V <sub>SS</sub> (V <sub>SS</sub> – V <sub>SSA</sub> )	-100	0	+100	mV	2
V <sub>ADIN</sub>	Input voltage	<ul style="list-style-type: none"> <li>16-bit differential mode</li> <li>All other modes</li> </ul>	VREFL VREFL	— —	31/32 * VREFH VREFH	V	—
C <sub>ADIN</sub>	Input capacitance	<ul style="list-style-type: none"> <li>16-bit mode</li> <li>8-bit / 10-bit / 12-bit modes</li> </ul>	— —	8 4	10 5	pF	—
R <sub>ADIN</sub>	Input series resistance		—	2	5	kΩ	—
R <sub>AS</sub>	Analog source resistance (external)	13-bit / 12-bit modes f <sub>ADCK</sub> < 4 MHz	—	—	5	kΩ	3
f <sub>ADCK</sub>	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f <sub>ADCK</sub>	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C <sub>rate</sub>	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C <sub>rate</sub>	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume V<sub>DDA</sub> = 3.0 V, Temp = 25 °C, f<sub>ADCK</sub> = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R<sub>AS</sub>/C<sub>AS</sub> time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the [ADC calculator tool](#).

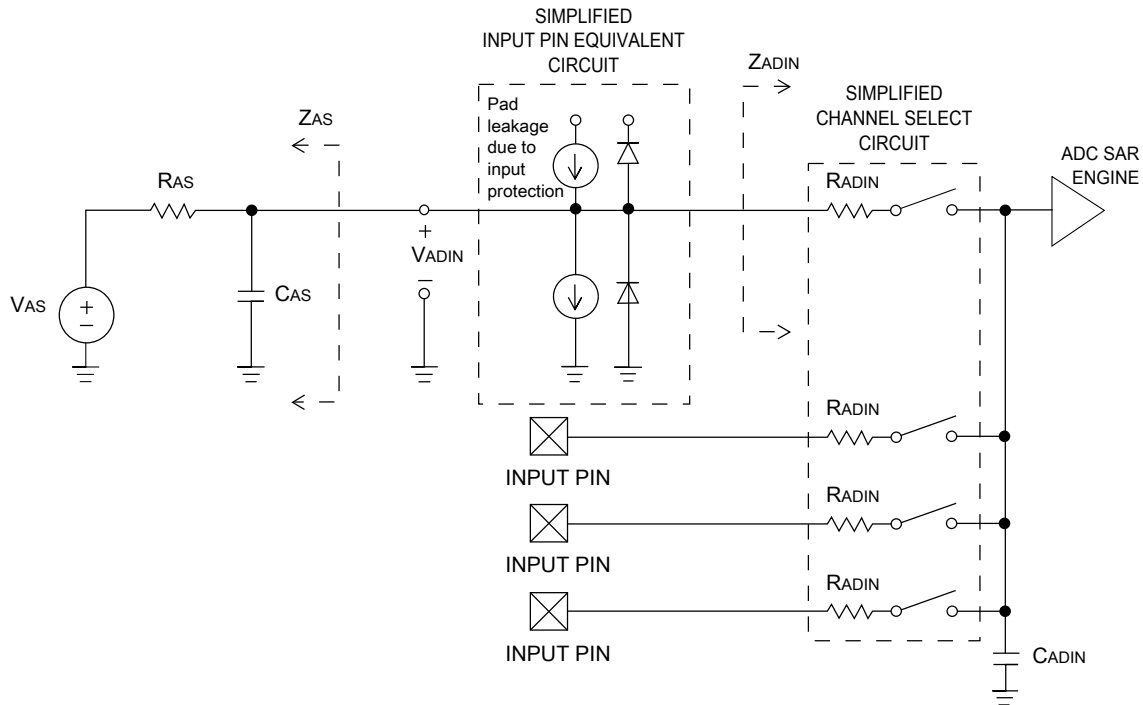


Figure 6. ADC input impedance equivalency diagram

### 3.6.1.2 16-bit ADC electrical characteristics

Table 26. 16-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ ,  $V_{REFL} = V_{SSA}$ )

Symbol	Description	Conditions <sup>1</sup>	Min.	Typ. <sup>2</sup>	Max.	Unit	Notes
I <sub>DDA_ADC</sub>	Supply current		0.215	—	1.7	mA	3
f <sub>ADACK</sub>	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	t <sub>ADACK</sub> = 1/f <sub>ADACK</sub>
		• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	
		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	<ul style="list-style-type: none"><li>• 12-bit modes</li><li>• &lt;12-bit modes</li></ul>	— —	±2.5 ±1.4	±6.8 ±2.1	LSB <sup>4</sup>	5
DNL	Differential non-linearity	<ul style="list-style-type: none"><li>• 12-bit modes</li><li>• &lt;12-bit modes</li></ul>	— —	±0.7 ±0.2	−1.1 to +1.9 −0.3 to 0.5	LSB <sup>4</sup>	5
INL	Integral non-linearity	<ul style="list-style-type: none"><li>• 12-bit modes</li></ul>	—	±0.9	−2.7 to +1.9	LSB <sup>4</sup>	5

Table continues on the next page...

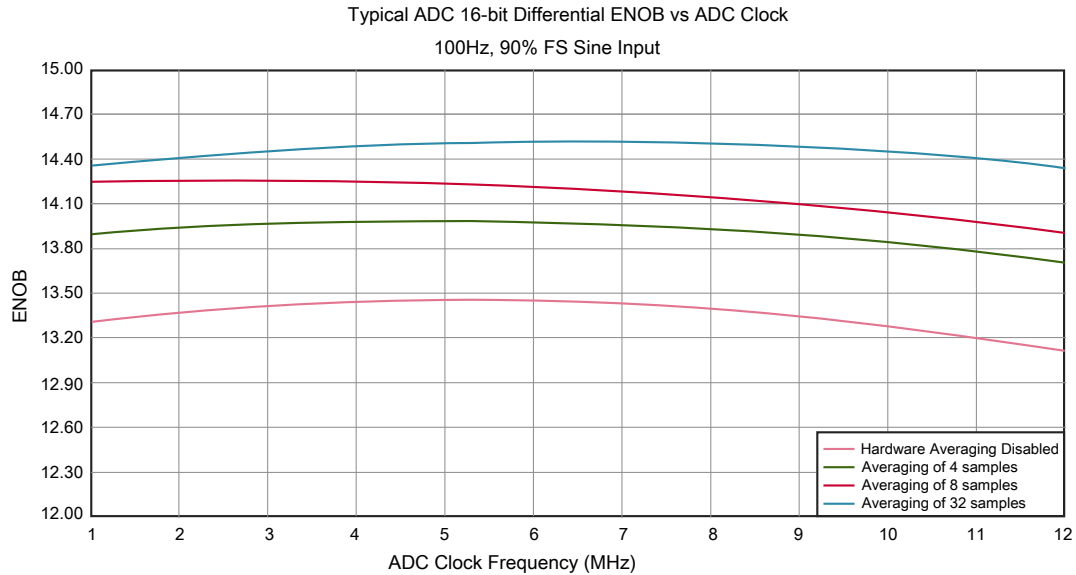
**Table 26. 16-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ ,  $V_{REFL} = V_{SSA}$ ) (continued)**

Symbol	Description	Conditions <sup>1</sup>	Min.	Typ. <sup>2</sup>	Max.	Unit	Notes
		<ul style="list-style-type: none"> <li>&lt;12-bit modes</li> </ul>	—	±0.4	−0.7 to +0.5		
$E_{FS}$	Full-scale error	<ul style="list-style-type: none"> <li>12-bit modes</li> <li>&lt;12-bit modes</li> </ul>	—	−4	−5.4	LSB <sup>4</sup>	$V_{ADIN} = V_{DDA}$ <sup>5</sup>
$E_Q$	Quantization error	<ul style="list-style-type: none"> <li>16-bit modes</li> <li>≤13-bit modes</li> </ul>	—	−1 to 0	—	LSB <sup>4</sup>	
$ENOB$	Effective number of bits	16-bit differential mode <ul style="list-style-type: none"> <li>Avg = 32</li> <li>Avg = 4</li> </ul> 16-bit single-ended mode <ul style="list-style-type: none"> <li>Avg = 32</li> <li>Avg = 4</li> </ul>	12.8 11.9	14.5 13.8	— —	bits bits	<sup>6</sup>
$SINAD$	Signal-to-noise plus distortion	See ENOB	$6.02 \times ENOB + 1.76$			dB	
$THD$	Total harmonic distortion	16-bit differential mode <ul style="list-style-type: none"> <li>Avg = 32</li> </ul> 16-bit single-ended mode <ul style="list-style-type: none"> <li>Avg = 32</li> </ul>	—	−94	—	dB	<sup>7</sup>
$SFDR$	Spurious free dynamic range	16-bit differential mode <ul style="list-style-type: none"> <li>Avg = 32</li> </ul> 16-bit single-ended mode <ul style="list-style-type: none"> <li>Avg = 32</li> </ul>	82 78	95 90	— —	dB dB	<sup>7</sup>
$E_{IL}$	Input leakage error		$I_{IN} \times R_{AS}$			mV	$I_{IN}$ = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	<sup>8</sup>
$V_{TEMP25}$	Temp sensor voltage	25 °C	706	716	726	mV	<sup>8</sup>

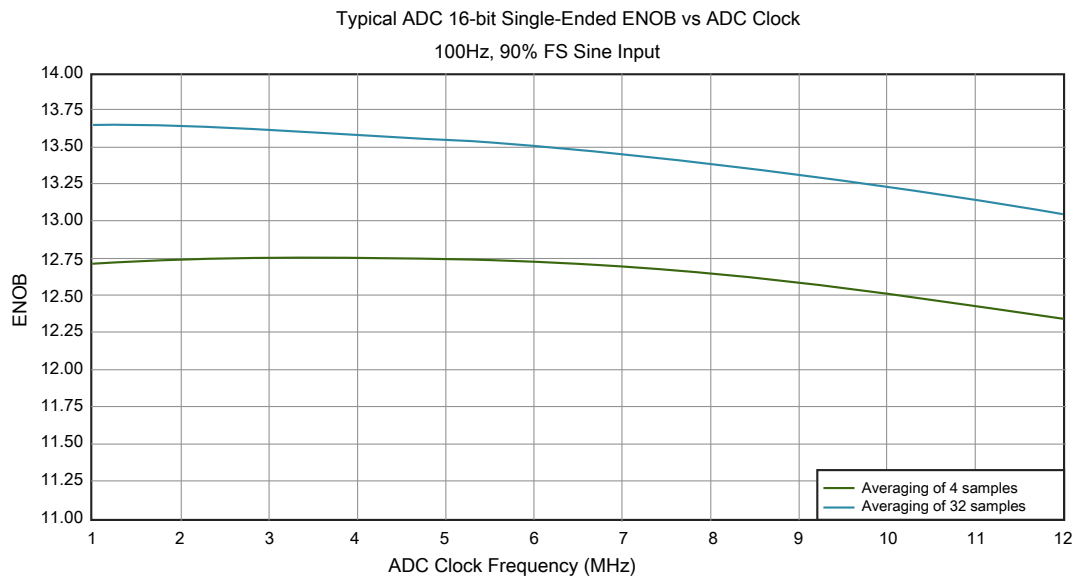
1. All accuracy numbers assume the ADC is calibrated with  $V_{REFH} = V_{DDA}$



2. Typical values assume  $V_{DDA} = 3.0\text{ V}$ ,  $\text{Temp} = 25\text{ }^{\circ}\text{C}$ ,  $f_{\text{ADCK}} = 2.0\text{ MHz}$  unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC\_CFG1[ADLPC] (low power). For lowest power operation, ADC\_CFG1[ADLPC] must be set, the ADC\_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4.  $1\text{ LSB} = (V_{\text{REFH}} - V_{\text{REFL}})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz



**Figure 7. Typical ENOB vs. ADC\_CLK for 16-bit differential mode**



**Figure 8. Typical ENOB vs. ADC\_CLK for 16-bit single-ended mode**

### 3.6.2 Voltage reference electrical specifications

**Table 27. VREF full-range operating requirements**

Symbol	Description	Min.	Max.	Unit	Notes
V <sub>DDA</sub>	Supply voltage		3.6	V	—
T <sub>A</sub>	Temperature	Operating temperature range of the device		°C	—
C <sub>L</sub>	Output load capacitance	100		nF	1, 2

1. C<sub>L</sub> must be connected to VREF\_OUT if the VREF\_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C<sub>L</sub> value over the operating temperature range of the device.

Table 28 is tested under the condition of setting VREF\_TRM[CHOPEN], VREF\_SC[REGEN] and VREF\_SC[ICOMPEN] bits to 1.

**Table 28. VREF full-range operating behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V <sub>out</sub>	Voltage reference output with factory trim at nominal V <sub>DDA</sub> and temperature=25°C	1.1915	1.195	1.1977	V	1
V <sub>out</sub>	Voltage reference output — factory trim	1.1584	—	1.2376	V	1
V <sub>out</sub>	Voltage reference output — user trim	1.193	—	1.197	V	1
V <sub>step</sub>	Voltage reference trim step	—	0.5	—	mV	1
V <sub>tdrift</sub>	Temperature drift (V <sub>max</sub> -V <sub>min</sub> across the full temperature range: 0 to 70°C)	—	2	15	mV	1
I <sub>bg</sub>	Bandgap only current	—	—	80	μA	1
I <sub>lp</sub>	Low-power buffer current	—	—	360	μA	1
I <sub>hp</sub>	High-power buffer current	—	—	1	mA	1
ΔV <sub>LOAD</sub>	Load regulation • current = ± 1.0 mA	—	200	—	μV	1, 2
T <sub>stup</sub>	Buffer startup time	—	—	100	μs	—
T <sub>chop_osc_st up</sub>	Internal bandgap start-up delay with chop oscillator enabled	—	—	35	ms	—
V <sub>vdri</sub>	Voltage drift (V <sub>max</sub> -V <sub>min</sub> across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF\_OUT voltage with no load vs. voltage with defined load

**Table 29. VREF limited-range operating requirements**

Symbol	Description	Min.	Max.	Unit	Notes
$T_A$	Temperature	0	50	°C	—

**Table 30. VREF limited-range operating behaviors**

Symbol	Description	Min.	Max.	Unit	Notes
$V_{out}$	Voltage reference output with factory trim	1.173	1.225	V	—

### 3.6.3 CMP and 6-bit DAC electrical specifications

**Table 31. Comparator and 6-bit DAC electrical specifications**

Symbol	Description	Min.	Typ.	Max.	Unit
$V_{DD}$	Supply voltage	1.71	—	3.6	V
$I_{DDHS}$	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
$I_{DDL S}$	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
$V_{AIN}$	Analog input voltage	$V_{SS} - 0.3$	—	$V_{DD}$	V
$V_{AIO}$	Analog input offset voltage	—	—	20	mV
$V_H$	Analog comparator hysteresis <sup>1</sup> <ul style="list-style-type: none"> <li>CR0[HYSTCTR] = 00</li> <li>CR0[HYSTCTR] = 01</li> <li>CR0[HYSTCTR] = 10</li> <li>CR0[HYSTCTR] = 11</li> </ul>	— — — —	5 10 20 30	— — — —	mV mV mV mV
$V_{CMPOH}$	Output high	$V_{DD} - 0.5$	—	—	V
$V_{CMPOI}$	Output low	—	—	0.5	V
$t_{DHS}$	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
$t_{DLS}$	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay <sup>2</sup>	—	—	40	μs
$I_{DAC6b}$	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	−0.5	—	0.5	LSB <sup>3</sup>
DNL	6-bit DAC differential non-linearity	−0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to  $V_{DD}-0.6$  V.

2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP\_DACCR[DACEN], CMP\_DACCR[VRSEL], CMP\_DACCR[VOSEL], CMP\_MUXCR[PSEL], and CMP\_MUXCR[MSEL]) and the comparator output settling to a stable level.

3. 1 LSB =  $V_{reference}/64$

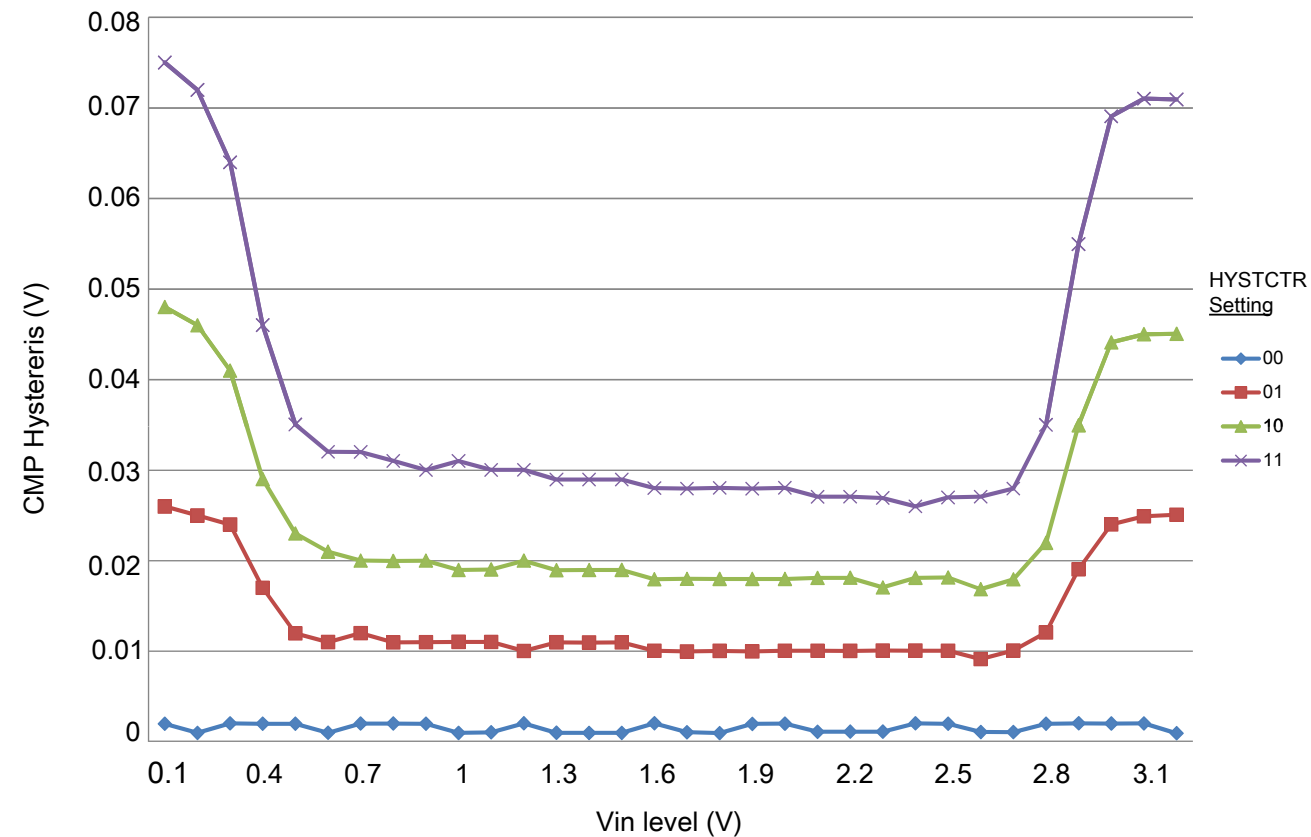


Figure 9. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

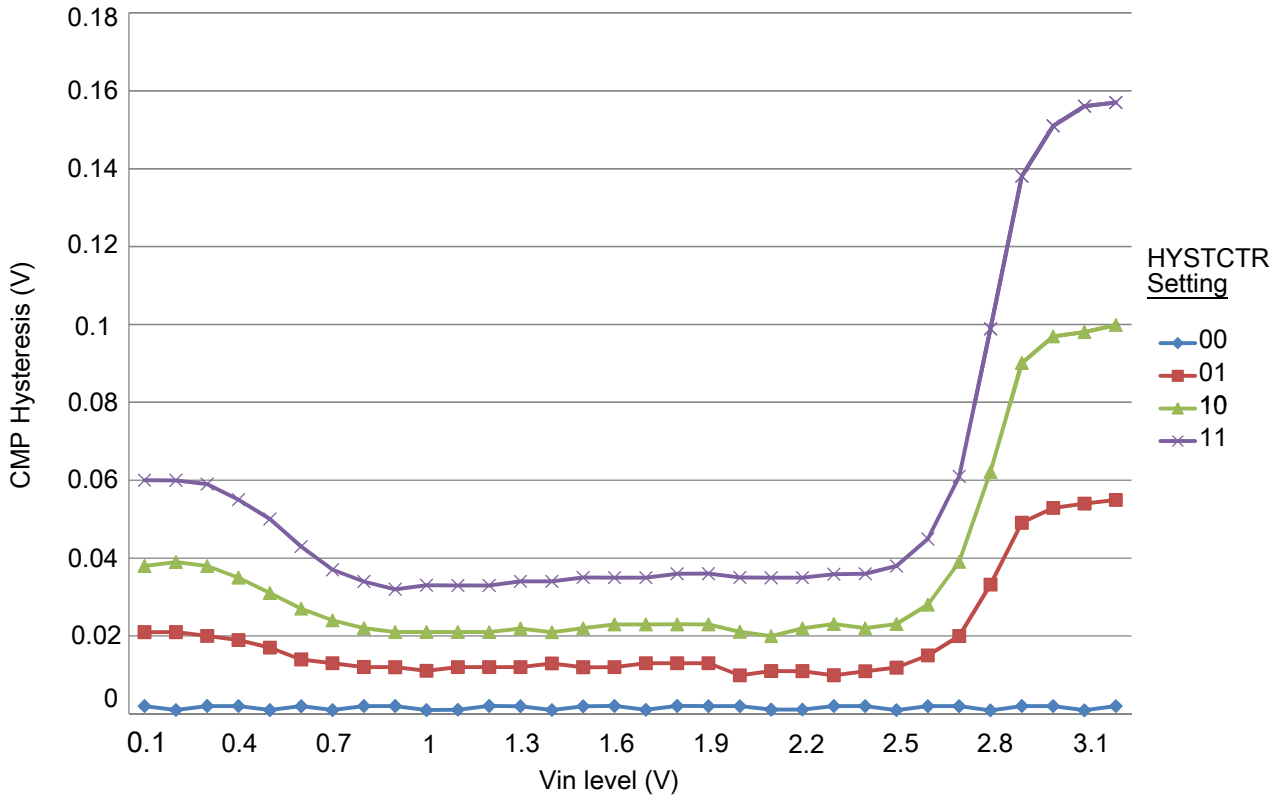


Figure 10. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

### 3.6.4 12-bit DAC electrical characteristics

#### 3.6.4.1 12-bit DAC operating requirements

Table 32. 12-bit DAC operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
$V_{DDA}$	Supply voltage		3.6	V	
$V_{DACR}$	Reference voltage	1.13	3.6	V	1
$C_L$	Output load capacitance	—	100	pF	2
$I_L$	Output load current	—	1	mA	

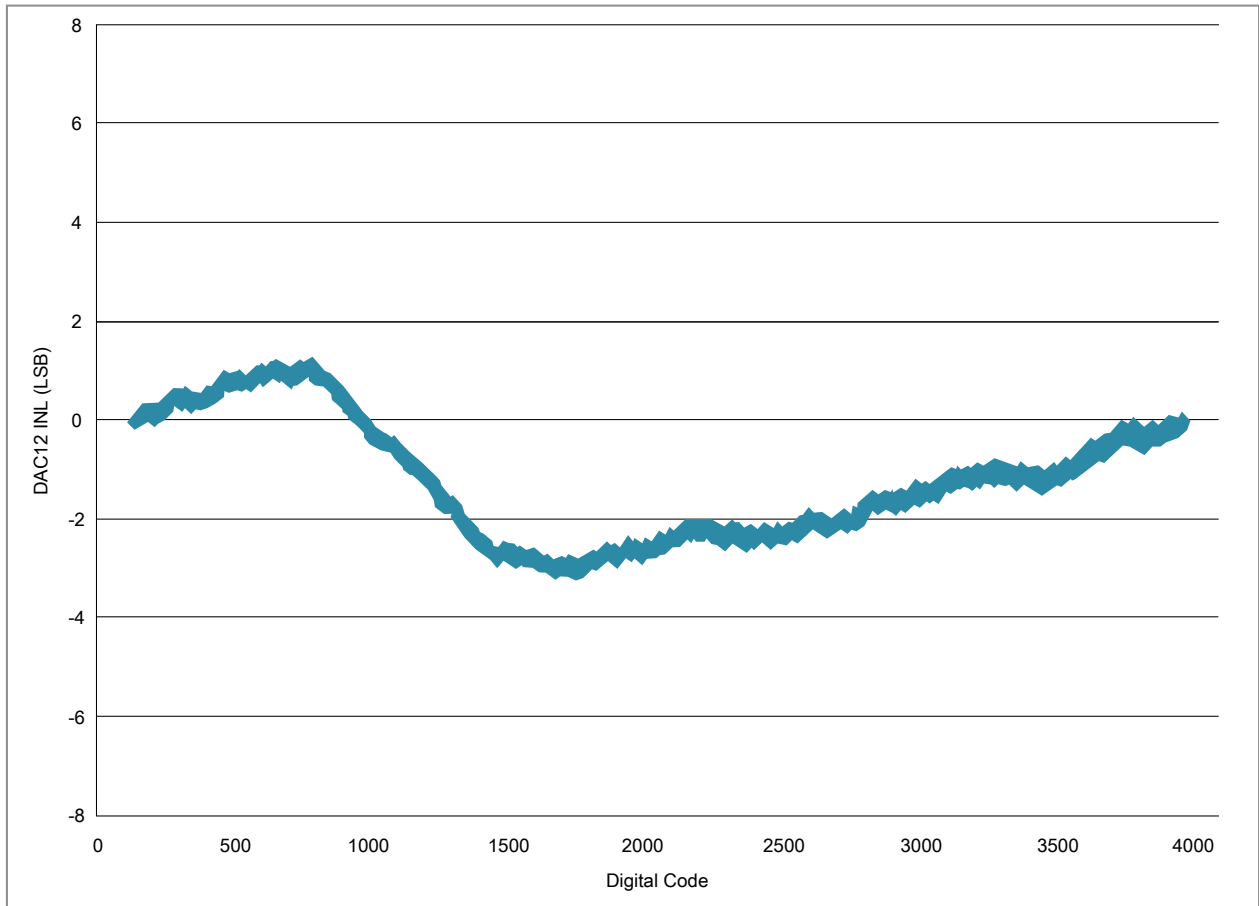
1. The DAC reference can be selected to be  $V_{DDA}$  or  $V_{REFH}$ .
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

### 3.6.4.2 12-bit DAC operating behaviors

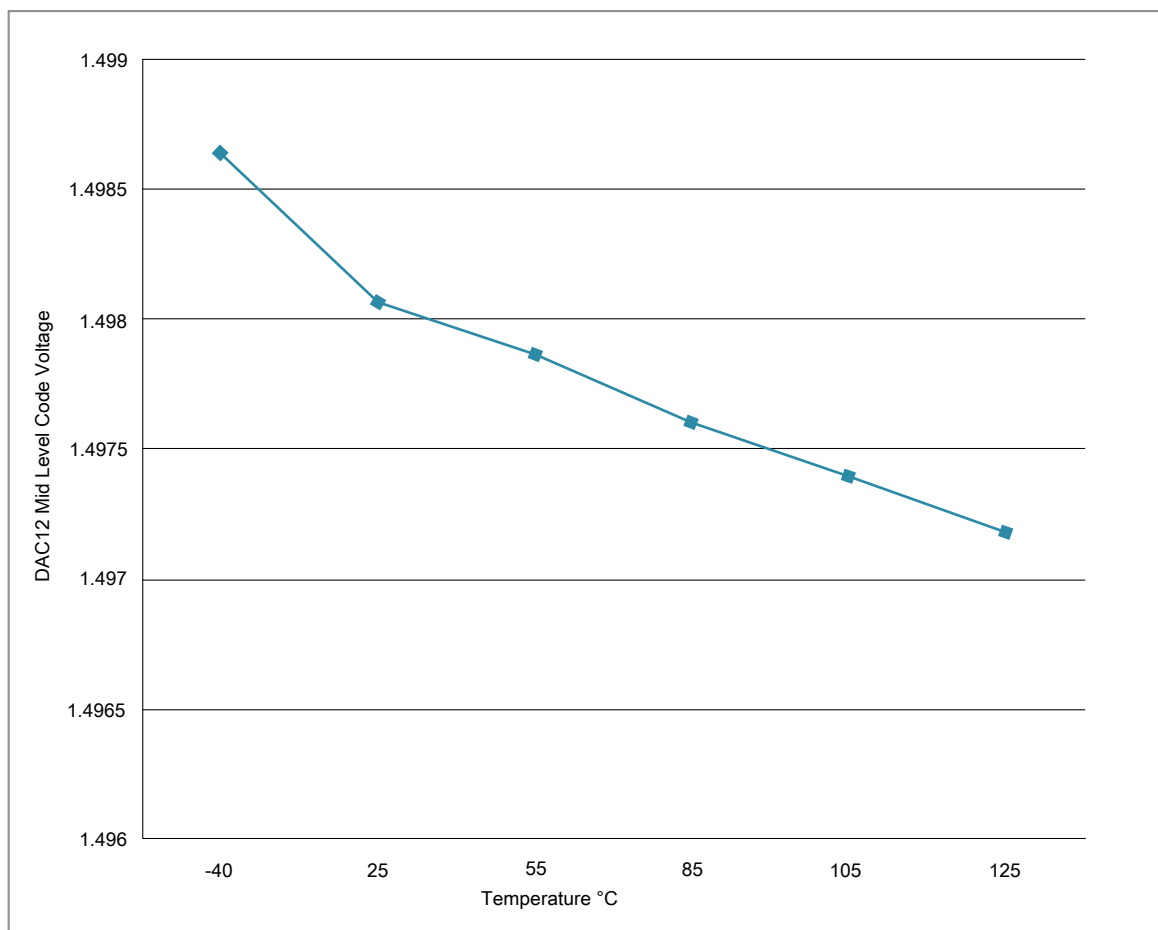
Table 33. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$I_{DDA\_DACLP}$	Supply current — low-power mode	—	—	250	$\mu A$	
$I_{DDA\_DACHP}$	Supply current — high-speed mode	—	—	900	$\mu A$	
$t_{DACLP}$	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	$\mu s$	1
$t_{DACHP}$	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	$\mu s$	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	$\mu s$	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	$V_{DACR} - 100$	—	$V_{DACR}$	mV	
INL	Integral non-linearity error — high speed mode	—	—	$\pm 8$	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2 V$	—	—	$\pm 1$	LSB	3
DNL	Differential non-linearity error — $V_{DACR} = V_{REF\_OUT}$	—	—	$\pm 1$	LSB	4
$V_{OFFSET}$	Offset error	—	$\pm 0.4$	$\pm 0.8$	%FSR	5
$E_G$	Gain error	—	$\pm 0.1$	$\pm 0.6$	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4 V$	60	—	90	dB	
$T_{CO}$	Temperature coefficient offset voltage	—	3.7	—	$\mu V/C$	6
$T_{GE}$	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
$R_{op}$	Output resistance (load = 3 k $\Omega$ )	—	—	250	$\Omega$	
SR	Slew rate -80h → F7Fh → 80h <ul style="list-style-type: none"> <li>High power (<math>SP_{HP}</math>)</li> <li>Low power (<math>SP_{LP}</math>)</li> </ul>	1.2 0.05	1.7 0.12	— —	V/ $\mu s$	
BW	3dB bandwidth <ul style="list-style-type: none"> <li>High power (<math>SP_{HP}</math>)</li> <li>Low power (<math>SP_{LP}</math>)</li> </ul>	550 40	— —	— —	kHz	

- Settling within  $\pm 1$  LSB
- The INL is measured for 0 + 100 mV to  $V_{DACR} - 100$  mV
- The DNL is measured for 0 + 100 mV to  $V_{DACR} - 100$  mV
- The DNL is measured for 0 + 100 mV to  $V_{DACR} - 100$  mV with  $V_{DDA} > 2.4 V$
- Calculated by a best fit curve from  $V_{SS} + 100$  mV to  $V_{DACR} - 100$  mV
- $V_{DDA} = 3.0 V$ , reference select set for  $V_{DDA}$  (DACx\_CO:DACRFS = 1), high power mode (DACx\_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device



**Figure 11. Typical INL error vs. digital code**



**Figure 12. Offset at half scale vs. temperature**

## 4 Timers

See [General switching specifications](#).

## 5 Communication interfaces



## 5.1 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20%  $V_{DD}$  and 80%  $V_{DD}$  thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

**Table 34. SPI master mode timing on slew rate disabled pads**

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	$t_{SPSCK}$	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	$t_{Lead}$	Enable lead time	1/2	—	$t_{SPSCK}$	—
4	$t_{Lag}$	Enable lag time	1/2	—	$t_{SPSCK}$	—
5	$t_{WSPSCK}$	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	$t_{SU}$	Data setup time (inputs)	18	—	ns	—
7	$t_{HI}$	Data hold time (inputs)	0	—	ns	—
8	$t_v$	Data valid (after SPSCK edge)	—	15	ns	—
9	$t_{HO}$	Data hold time (outputs)	0	—	ns	—
10	$t_{RI}$	Rise time input	—	$t_{periph} - 25$	ns	—
	$t_{FI}$	Fall time input				
11	$t_{RO}$	Rise time output	—	25	ns	—
	$t_{FO}$	Fall time output				

1. For SPI0  $f_{periph}$  is the bus clock ( $f_{BUS}$ ). For SPI1  $f_{periph}$  is the system clock ( $f_{SYS}$ ).
2.  $t_{periph} = 1/f_{periph}$

**Table 35. SPI master mode timing on slew rate enabled pads**

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	$t_{SPSCK}$	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	$t_{Lead}$	Enable lead time	1/2	—	$t_{SPSCK}$	—
4	$t_{Lag}$	Enable lag time	1/2	—	$t_{SPSCK}$	—
5	$t_{WSPSCK}$	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	$t_{SU}$	Data setup time (inputs)	96	—	ns	—
7	$t_{HI}$	Data hold time (inputs)	0	—	ns	—

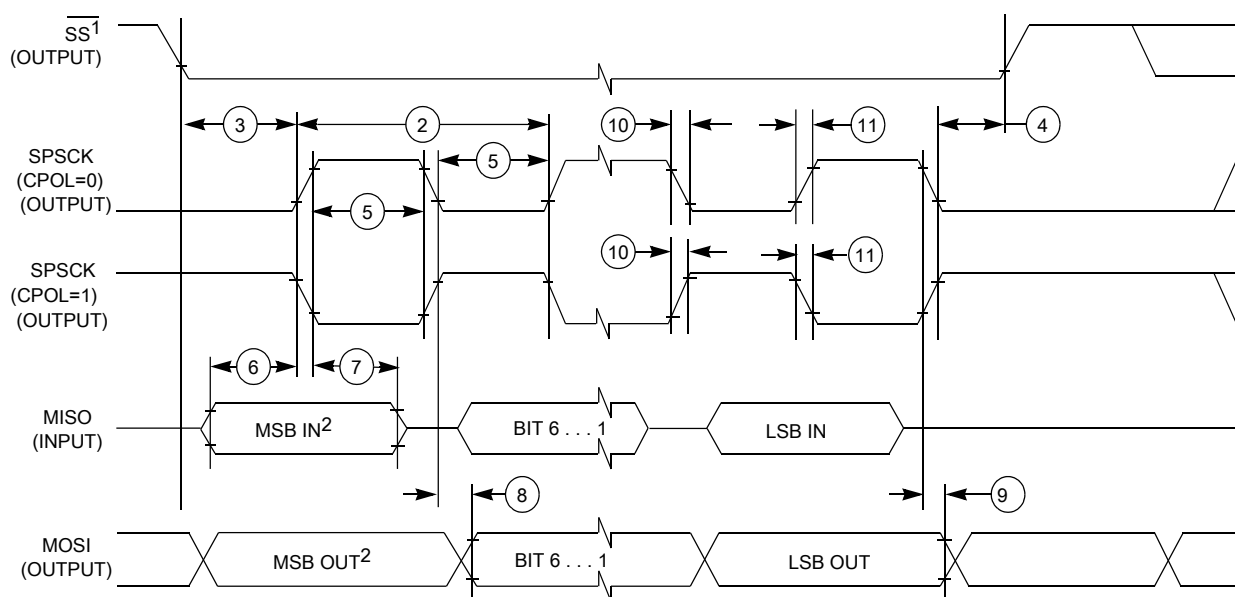
*Table continues on the next page...*

**Table 35. SPI master mode timing on slew rate enabled pads (continued)**

Num.	Symbol	Description	Min.	Max.	Unit	Note
8	$t_v$	Data valid (after SPSCCK edge)	—	83	ns	—
9	$t_{HO}$	Data hold time (outputs)	0	—	ns	—
10	$t_{RI}$	Rise time input	—	$t_{\text{periph}} - 25$	ns	—
	$t_{FI}$	Fall time input				
11	$t_{RO}$	Rise time output	—	36	ns	—
	$t_{FO}$	Fall time output				

1. For SPI0  $f_{\text{periph}}$  is the bus clock ( $f_{\text{BUS}}$ ). For SPI1  $f_{\text{periph}}$  is the system clock ( $f_{\text{SYS}}$ ).

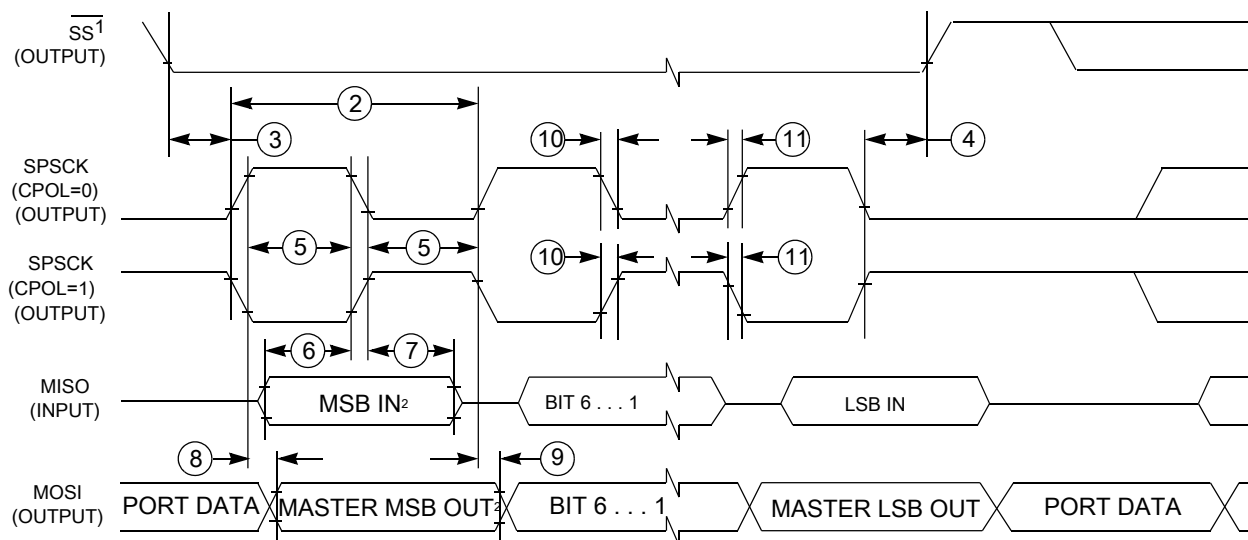
2.  $t_{\text{periph}} = 1/f_{\text{periph}}$



1. If configured as an output.

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

**Figure 13. SPI master mode timing (CPHA = 0)**



1. If configured as output

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

**Figure 14. SPI master mode timing (CPHA = 1)**

**Table 36. SPI slave mode timing on slew rate disabled pads**

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	$t_{SPSCCK}$	SPSCCK period	$4 \times t_{periph}$	—	ns	2
3	$t_{Lead}$	Enable lead time	1	—	$t_{periph}$	—
4	$t_{Lag}$	Enable lag time	1	—	$t_{periph}$	—
5	$t_{WSPSCCK}$	Clock (SPSCCK) high or low time	$t_{periph} - 30$	—	ns	—
6	$t_{SU}$	Data setup time (inputs)	2.5	—	ns	—
7	$t_{HI}$	Data hold time (inputs)	3.5	—	ns	—
8	$t_a$	Slave access time	—	$t_{periph}$	ns	3
9	$t_{dis}$	Slave MISO disable time	—	$t_{periph}$	ns	4
10	$t_v$	Data valid (after SPSCCK edge)	—	31	ns	—
11	$t_{HO}$	Data hold time (outputs)	0	—	ns	—
12	$t_{RI}$	Rise time input	—	$t_{periph} - 25$	ns	—
	$t_{FI}$	Fall time input				
13	$t_{RO}$	Rise time output	—	25	ns	—
	$t_{FO}$	Fall time output				

1. For SPI0  $f_{periph}$  is the bus clock ( $f_{BUS}$ ). For SPI1  $f_{periph}$  is the system clock ( $f_{SYS}$ ).

2.  $t_{periph} = 1/f_{periph}$

3. Time to data active from high-impedance state

4. Hold time to high-impedance state

**Table 37. SPI slave mode timing on slew rate enabled pads**

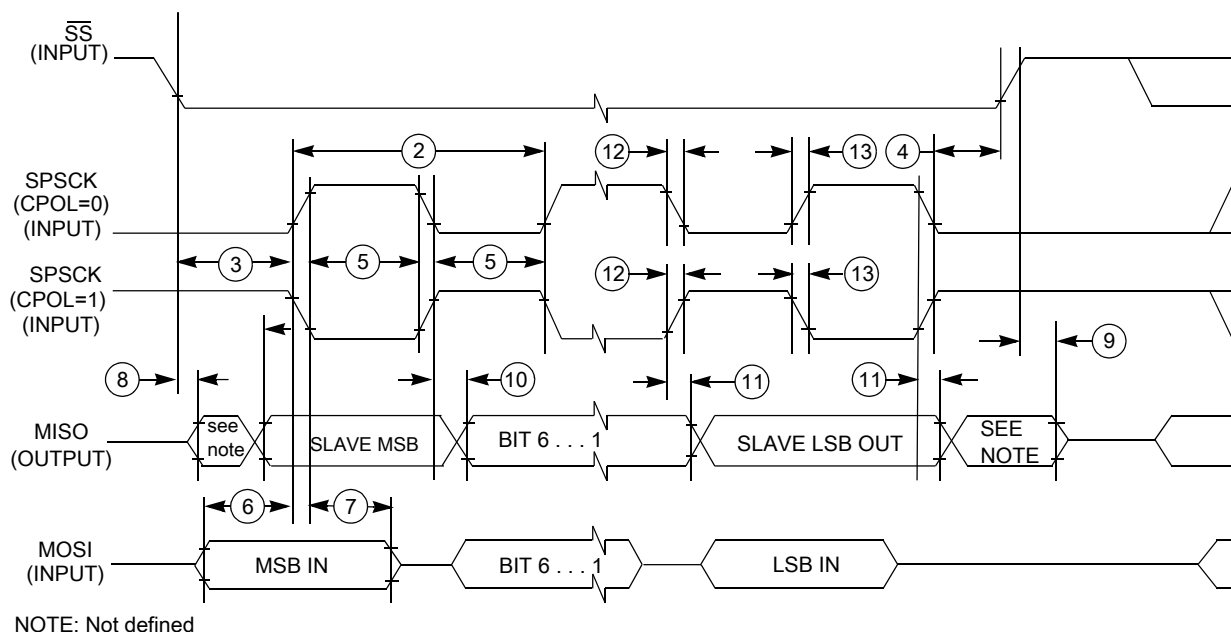
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	$f_{op}$	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	$t_{SPSCK}$	SPSCK period	$4 \times t_{periph}$	—	ns	2
3	$t_{Lead}$	Enable lead time	1	—	$t_{periph}$	—
4	$t_{Lag}$	Enable lag time	1	—	$t_{periph}$	—
5	$t_{WSPSCK}$	Clock (SPSCK) high or low time	$t_{periph} - 30$	—	ns	—
6	$t_{SU}$	Data setup time (inputs)	2	—	ns	—
7	$t_{HI}$	Data hold time (inputs)	7	—	ns	—
8	$t_a$	Slave access time	—	$t_{periph}$	ns	3
9	$t_{dis}$	Slave MISO disable time	—	$t_{periph}$	ns	4
10	$t_v$	Data valid (after SPSCK edge)	—	130	ns	—
11	$t_{HO}$	Data hold time (outputs)	0	—	ns	—
12	$t_{RI}$	Rise time input	—	$t_{periph} - 25$	ns	—
	$t_{FI}$	Fall time input				
13	$t_{RO}$	Rise time output	—	36	ns	—
	$t_{FO}$	Fall time output				

1. For SPI0  $f_{periph}$  is the bus clock ( $f_{BUS}$ ). For SPI1  $f_{periph}$  is the system clock ( $f_{SYS}$ ).

2.  $t_{periph} = 1/f_{periph}$

3. Time to data active from high-impedance state

4. Hold time to high-impedance state

**Figure 15. SPI slave mode timing (CPHA = 0)**

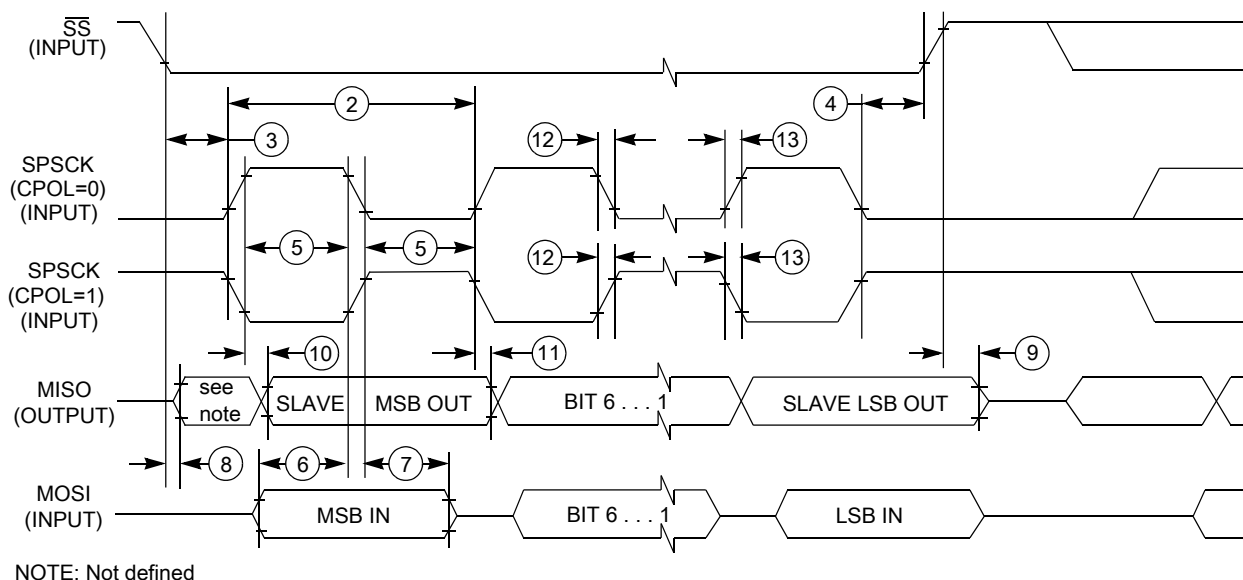


Figure 16. SPI slave mode timing (CPHA = 1)

## 5.2 I<sup>2</sup>C

### 5.2.1 Inter-Integrated Circuit Interface (I<sup>2</sup>C) timing

Table 38. I<sup>2</sup>C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	$f_{SCL}$	0	100	0	400 <sup>1</sup>	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	$t_{HD}; STA$	4	—	0.6	—	$\mu s$
LOW period of the SCL clock	$t_{LOW}$	4.7	—	1.25	—	$\mu s$
HIGH period of the SCL clock	$t_{HIGH}$	4	—	0.6	—	$\mu s$
Set-up time for a repeated START condition	$t_{SU}; STA$	4.7	—	0.6	—	$\mu s$
Data hold time for I <sup>2</sup> C bus devices	$t_{HD}; DAT$	0 <sup>2</sup>	3.45 <sup>3</sup>	0 <sup>4</sup>	0.9 <sup>2</sup>	$\mu s$
Data set-up time	$t_{SU}; DAT$	250 <sup>5</sup>	—	100 <sup>3, 6</sup>	—	ns
Rise time of SDA and SCL signals	$t_r$	—	1000	$20 + 0.1C_b$ <sup>7</sup>	300	ns
Fall time of SDA and SCL signals	$t_f$	—	300	$20 + 0.1C_b$ <sup>6</sup>	300	ns
Set-up time for STOP condition	$t_{SU}; STO$	4	—	0.6	—	$\mu s$
Bus free time between STOP and START condition	$t_{BUF}$	4.7	—	1.3	—	$\mu s$
Pulse width of spikes that must be suppressed by the input filter	$t_{SP}$	N/A	N/A	0	50	ns

## Communication interfaces

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only be achieved when using the High drive pins across the full voltage range and when using the Normal drive pins and  $VDD \geq 2.7$  V.
2. The master mode I<sup>2</sup>C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
3. The maximum t<sub>HD</sub>; DAT must be met only if the device does not stretch the LOW period (t<sub>LOW</sub>) of the SCL signal.
4. Input signal Slew = 10 ns and Output Load = 50 pF
5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
6. A Fast mode I<sup>2</sup>C bus device can be used in a Standard mode I<sup>2</sup>C bus system, but the requirement t<sub>SU</sub>; DAT  $\geq$  250 ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line t<sub>rmax</sub> + t<sub>SU</sub>; DAT = 1000 + 250 = 1250 ns (according to the Standard mode I<sup>2</sup>C bus specification) before the SCL line is released.
7. C<sub>b</sub> = total capacitance of the one bus line in pF.

To achieve 1MHz I2C clock rates, consider the following recommendations:

- To counter the effects of clock stretching, the I2C baud Rate select bits can be configured for faster than desired baud rate.
- Use high drive pad and DSE bit should be set in PORTx\_PCRn register.
- Minimize loading on the I2C SDA and SCL pins to ensure fastest rise times for the SCL line to avoid clock stretching.
- Use smaller pull up resistors on SDA and SCL to reduce the RC time constant.

**Table 39. I<sup>2</sup>C 1Mbit/s timing**

Characteristic	Symbol	Minimum	Maximum	Unit
SCL Clock Frequency	f <sub>SCL</sub>	0	1 <sup>1</sup>	MHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t <sub>HD</sub> ; STA	0.26	—	μs
LOW period of the SCL clock	t <sub>LOW</sub>	0.5	—	μs
HIGH period of the SCL clock	t <sub>HIGH</sub>	0.26	—	μs
Set-up time for a repeated START condition	t <sub>SU</sub> ; STA	0.26	—	μs
Data hold time for I <sup>2</sup> C bus devices	t <sub>HD</sub> ; DAT	0	—	μs
Data set-up time	t <sub>SU</sub> ; DAT	50	—	ns
Rise time of SDA and SCL signals	t <sub>r</sub>	20 + 0.1C <sub>b</sub>	120	ns
Fall time of SDA and SCL signals	t <sub>f</sub>	20 + 0.1C <sub>b</sub> <sup>2</sup>	120	ns
Set-up time for STOP condition	t <sub>SU</sub> ; STO	0.26	—	μs
Bus free time between STOP and START condition	t <sub>BUF</sub>	0.5	—	μs
Pulse width of spikes that must be suppressed by the input filter	t <sub>SP</sub>	0	50	ns

1. The maximum SCL Clock Frequency of 1Mbit/s can support maximum bus loading when using the High drive pins across the full voltage range.
2. C<sub>b</sub> = total capacitance of the one bus line in pF.



### 6.1.2 Power delivery system

Consider the following items in the power delivery system:

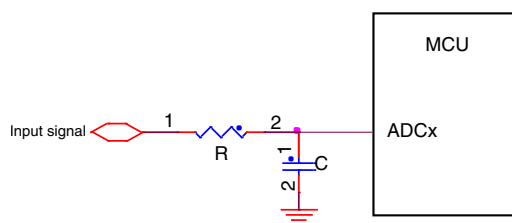
- Use a plane for ground.
- Use a plane for MCU VDD supply if possible.
- Always route ground first, as a plane or continuous surface, and never as sequential segments.
- Route power next, as a plane or traces that are parallel to ground traces.
- Place bulk capacitance, 10uF or more, at the entrance of the power plane.
- Place bypass capacitors for MCU power domain as close as possible to each VDD/VSS pair, including VDDA/VSSA and VREFH/VREFL.
- The minimum bypass requirement is to place 0.1  $\mu$ F capacitors positioned as near as possible to the package supply pins.
- Take special care to minimize noise levels on the VREFH/VREFL inputs. An option is to use the internal reference voltage (output 1.2V typically) as the ADC reference.

#### NOTE

The internal reference voltage output (VREFO) is bonded to the VREFH pin on some packages and to PTE30 on other packages. When the VREFO output is used, a 0.1uF capacitor is required as a filter. Do not connect any other supply voltage to the pin that has VREFO activated.

### 6.1.3 Analog design

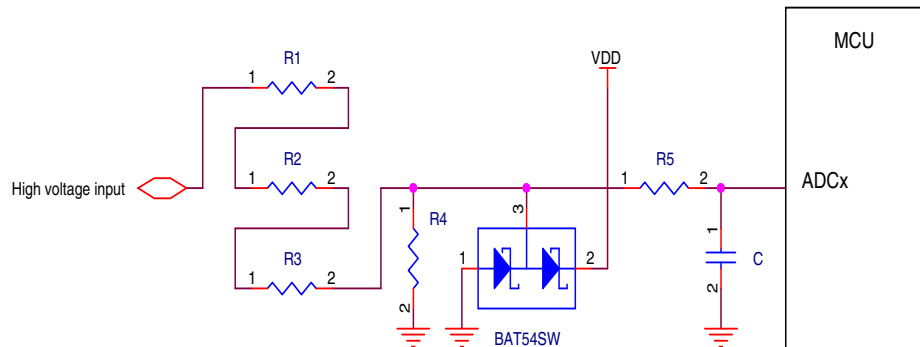
Each ADC input must have an RC filter as shown in the following figure. The maximum value of R must be RAS max if fast sampling and high resolution are required. The value of C must be chosen to ensure that the RC time constant is very small compared to the sample period.



**Figure 18. RC circuit for ADC input**



High voltage measurement circuits require voltage division, current limiting, and over-voltage protection as shown the following figure. The voltage divider formed by R1 – R4 must yield a voltage less than or equal to VREFH. The current must be limited to less than the injection current limit. Since the ADC pins do not have diodes to VDD, external clamp diodes must be included to protect against transient over-voltages.



**Figure 19. High voltage measurement with an ADC input**

### 6.1.4 Digital design

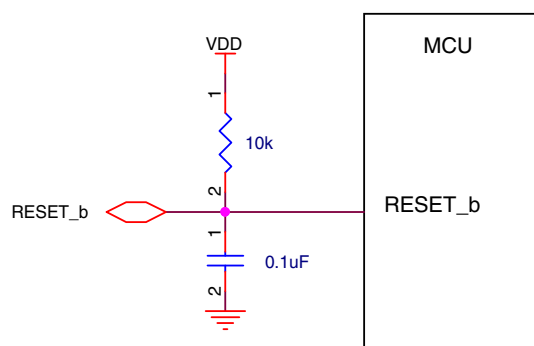
Ensure that all I/O pins cannot get pulled above VDD (max I/O spec is VDD+0.3V).

#### CAUTION

Do not provide power to I/O pins prior to VDD, especially the RESET\_b pin.

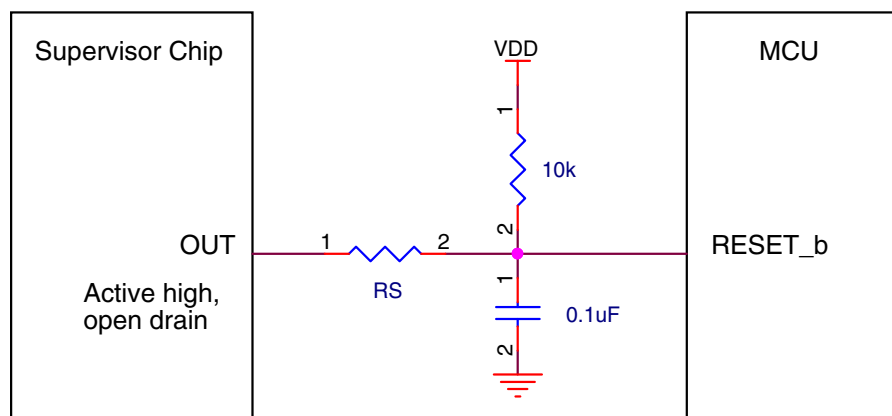
- RESET\_b pin

The RESET\_b pin is an open-drain I/O pin that has an internal pullup resistor. An external RC circuit is recommended to filter noise as shown in the following figure. The resistor value must be in the range of 4.7 kΩ to 10 kΩ; the recommended capacitance value is 0.1 μF. The RESET\_b pin also has a selectable digital filter to reject spurious noise.



**Figure 20. Reset circuit**

When an external supervisor chip is connected to the RESET\_b pin, a series resistor should be used to avoid damaging the supervisor chip or the RESET\_b pin, as shown in Figure 55. The series resistor value ( $R_S$  below) should be in the range of  $100\Omega$  to  $1k\Omega$  depending on the external reset chip drive strength. The supervisor chip must have an active high, open-drain output.

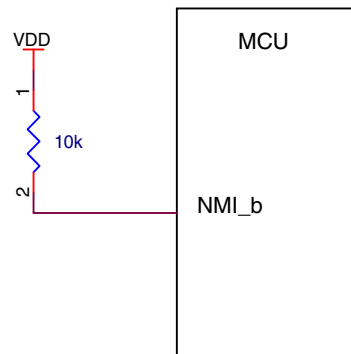


**Figure 21. Reset signal connection to external reset chip**

- NMI pin

Because a low level on the NMI\_b pin will trigger the Non-maskable interrupt, it is not recommended to add a pull-down resistor or capacitor on this pin. When this pin is enabled as the NMI function an external pull-up resistor (10k) as shown in the following figure is recommended for robustness.

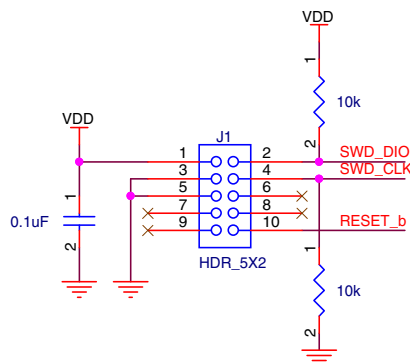
If the NMI\_b pin is used as an I/O pin the Non-maskable interrupt handler is required to disable the NMI function by remapping to another function. The NMI function is disabled by programming the FOPT[NMI\_DIS] bit to zero.



**Figure 22. NMI pin biasing**

- Debug interface

This MCU uses the standard ARM SWD interface protocol as shown in the following figure. While pull-up or pull-down resistors are not required (SWD\_DIO has an internal pull-up and SWD\_CLK has an internal pull-down), external 10kΩ pull resistors are recommended for system robustness. Please note the RESET\_b pin recommendations mentioned above.



**Figure 23. SWD debug interface**

- Low leakage stop mode wakeup

Select low leakage wakeup pins (LLWU\_Px) to wake the MCU from one of the low leakage stop modes (LLS/VLLSx). Please refer to the signal multiplexing table for pin selection.

- Unused pin

Unused GPIO pins should be left floating (no electrical connections) with the MUX field of the pin's PORTx\_PCRn register equal to 0:0:0. This disables the digital input path to the MCU.

### 6.1.5 Crystal oscillator

When using an external crystal or ceramic resonator as the frequency reference for the MCU clock system, refer to the following table and diagrams.

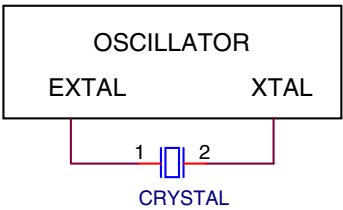
The feedback resistor,  $R_F$ , is incorporated internally with the low power oscillators. An external feedback is required when using high gain ( $HGO=1$ ) mode.

The series resistor,  $R_S$ , is required in high gain ( $HGO=1$ ) mode when the crystal or resonator frequency is below 2MHz. Otherwise, the low power oscillator ( $HGO=0$ ) must not have any series resistance; and the high frequency, high gain oscillator with a frequency above 2MHz does not require any series resistance.

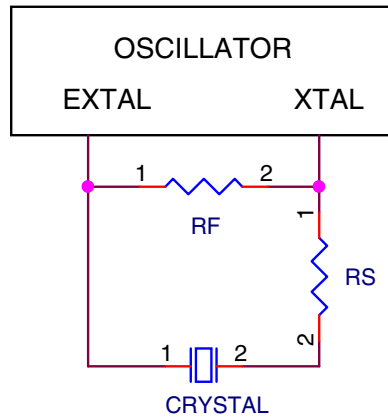
Internal load capacitors ( $C_x$ ,  $C_y$ ) are provided in the low frequency (32.768kHz) mode. Use the  $SCxP$  bits in the  $OSC0\_CR$  register to adjust the load capacitance for the crystal. Typically, values of 10pf to 16pF are sufficient for 32.768kHz crystals that have a 12.5pF CL specification. The internal load capacitor selection must not be used for high frequency crystals and resonators.

**Table 40. External crystal/resonator connections**

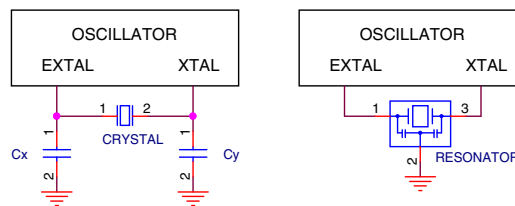
Oscillator mode	Oscillator mode
Low frequency (32.768kHz), low power	Diagram 1
Low frequency (32.768kHz), high gain	Diagram 2, Diagram 4
High frequency (1-32MHz), low power	Diagram 3
High frequency (1-32MHz), high gain	Diagram 4



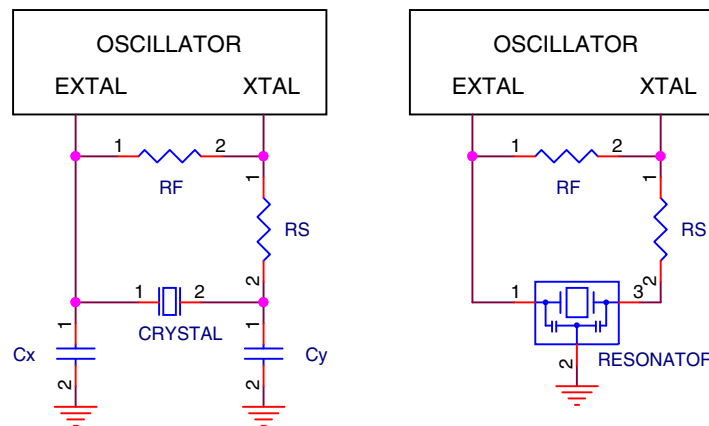
**Figure 24. Crystal connection – Diagram 1**



**Figure 25. Crystal connection – Diagram 2**



**Figure 26. Crystal connection – Diagram 3**



**Figure 27. Crystal connection – Diagram 4**

## 6.2 Software considerations

All Kinetis MCUs are supported by comprehensive Freescale and third-party hardware and software enablement solutions, which can reduce development costs and time to market. Featured software and tools are listed below. Visit <http://www.freescale.com/kinetis/sw> for more information and supporting collateral.

### Evaluation and Prototyping Hardware

## Human-machine interfaces (HMI)

- Freescale Freedom Development Platform: <http://www.freescale.com/freedom>
- Tower System Development Platform: <http://www.freescale.com/tower>

## IDEs for Kinetis MCUs

- Kinetis Design Studio IDE: <http://www.freescale.com/kds>
- Partner IDEs: <http://www.freescale.com/kide>

## Development Tools

- PEG Graphics Software: <http://www.freescale.com/peg>
- Processor Expert Software and Embedded Components: <http://www.freescale.com/processorexpert> )

## Run-time Software

- Kinetis SDK: <http://www.freescale.com/ksdk>
- Kinetis Bootloader: <http://www.freescale.com/kboot>
- ARM mbed Development Platform: <http://www.freescale.com/mbed>
- MQX RTOS: <http://www.freescale.com/mqx>

For all other partner-developed software and tools, visit <http://www.freescale.com/partners>.

# 7 Human-machine interfaces (HMI)

## 7.1 LCD electrical characteristics

Table 41. LCD electricals

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$f_{\text{Frame}}$	LCD frame frequency <ul style="list-style-type: none"><li>• GCR[FFR]=0</li><li>• GCR[FFR]=1</li></ul>	23.3	—	73.1	Hz	
		46.6	—	146.2	Hz	
$C_{\text{LCD}}$	LCD charge pump capacitance — nominal value	—	100	—	nF	
$C_{\text{BYLCD}}$	LCD bypass capacitance — nominal value	—	100	—	nF	1
$C_{\text{Glass}}$	LCD glass capacitance	—	2000	8000	pF	2
$V_{\text{IREG}}$	$V_{\text{IREG}}$ <ul style="list-style-type: none"><li>• RVTRIM=0000</li><li>• RVTRIM=1000</li></ul>	—	0.91	—	V	3
		—	0.92	—		

Table continues on the next page...

Table 41. LCD electricals (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> <li>RVTRIM=0100</li> <li>RVTRIM=1100</li> <li>RVTRIM=0010</li> <li>RVTRIM=1010</li> <li>RVTRIM=0110</li> <li>RVTRIM=1110</li> <li>RVTRIM=0001</li> <li>RVTRIM=1001</li> <li>RVTRIM=0101</li> <li>RVTRIM=1101</li> <li>RVTRIM=0011</li> <li>RVTRIM=1011</li> <li>RVTRIM=0111</li> <li>RVTRIM=1111</li> </ul>	—	0.93	—		
		—	0.94	—		
		—	0.96	—		
		—	0.97	—		
		—	0.98	—		
		—	0.99	—		
		—	1.01	—		
		—	1.02	—		
		—	1.03	—		
		—	1.05	—		
		—	1.06	—		
		—	1.07	—		
		—	1.08	—		
		—	1.09	—		
$\Delta_{RTRIM}$	V <sub>I<sub>REG</sub></sub> TRIM resolution	—	—	3.0	% V <sub>I<sub>REG</sub></sub>	
I <sub>V<sub>REG</sub></sub>	V <sub>I<sub>REG</sub></sub> current adder — RVEN = 1	—	1	—	μA	
I <sub>RBIAS</sub>	RBIAS current adder					
	<ul style="list-style-type: none"> <li>LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF)</li> </ul>	—	10	—	μA	
	<ul style="list-style-type: none"> <li>LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF)</li> </ul>	—	1	—	μA	
R <sub>RBIAS</sub>	RBIAS resistor values					
	<ul style="list-style-type: none"> <li>LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF)</li> </ul>	—	0.28	—	MΩ	
	<ul style="list-style-type: none"> <li>LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF)</li> </ul>	—	2.98	—	MΩ	
VLL1	VLL1 voltage	—	—	V <sub>I<sub>REG</sub></sub>	V	4
VLL2	VLL2 voltage	—	—	2 x V <sub>I<sub>REG</sub></sub>	V	4
VLL3	VLL3 voltage	—	—	3 x V <sub>I<sub>REG</sub></sub>	V	4
VLL1	VLL1 voltage	—	—	V <sub>DDA</sub> / 3	V	5
VLL2	VLL2 voltage	—	—	V <sub>DDA</sub> / 1.5	V	5
VLL3	VLL3 voltage	—	—	V <sub>DDA</sub>	V	5

1. The actual value used could vary with tolerance.
2. For highest glass capacitance values, LCD\_GCR[LADJ] should be configured as specified in the LCD Controller chapter within the device's reference manual.
3. V<sub>I<sub>REG</sub></sub> maximum should never be externally driven to any level other than V<sub>DD</sub> - 0.15 V
4. VLL1, VLL2 and VLL3 are a function of V<sub>I<sub>REG</sub></sub> only when the regulator is enabled (GCR[RVEN]=1) and the charge pump is enabled (GCR[CPSEL]=1).
5. VLL1, VLL2 and VLL3 are a function of V<sub>DDA</sub> only under either of the following conditions:

## Dimensions

- The charge pump is enabled (GCR[CPSEL]=1), the regulator is disabled (GCR[RVEN]=0), and VLL3 = V<sub>DDA</sub> through the internal power switch (GCR[VSUPPLY]=0).
- The resistor bias string is enabled (GCR[CPSEL]=0), the regulator is disabled (GCR[RVEN]=0), and VLL3 is connected to V<sub>DDA</sub> externally (GCR[VSUPPLY]=1).

# 8 Dimensions

## 8.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to [freescale.com](http://freescale.com) and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
48-pin QFN	98ASA00616D
64-pin LQFP	98ASS23234W
64-pin MAPBGA	98ASA00420D
80-pin LQFP	98ASS23174W

# 9 Pinouts and Packaging

## 9.1 KL33 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

### NOTE

The 48 QFN and 64 MAPBGA packages for this product are not yet available. However, these packages are included in Package Your Way program for Kinetis MCUs. Visit [freescale.com/KPYW](http://freescale.com/KPYW) for more details.

80 LQFP	64 LQFP	48 QFN	64 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
—	—	—	E4	VDD	VDD	VDD							



80 LQFP	64 LQFP	48 QFN	64 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	1	1	A1	PTE0	DISABLED	LCD_P48	PTE0/ CLKOUT32K	SPI1_MISO	LPUART1_ TX	RTC_ CLKOUT	CMP0_OUT	I2C1_SDA	LCD_P48
2	2	2	B1	PTE1	DISABLED	LCD_P49	PTE1	SPI1_MOSI	LPUART1_ RX		SPI1_MISO	I2C1_SCL	LCD_P49
3	—	—	—	PTE2	DISABLED	LCD_P50	PTE2	SPI1_SCK					LCD_P50
4	—	—	—	PTE3	DISABLED	LCD_P51	PTE3	SPI1_MISO			SPI1_MOSI		LCD_P51
5	—	—	—	PTE4	DISABLED	LCD_P52	PTE4	SPI1_PCS0					LCD_P52
6	—	—	—	PTE5	DISABLED	LCD_P53	PTE5						LCD_P53
7	3	—	—	VDD	VDD	VDD							
8	4	—	C4	VSS	VSS	VSS							
9	5	3	E1	PTE16	ADC0_DP1/ ADC0_SE1	LCD_P55/ ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_ CLKIN0		FXIO0_D0	LCD_P55
10	6	4	D1	PTE17	ADC0_DM1/ ADC0_SE5a	LCD_P56/ ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_ CLKIN1	LPTMR0_ ALT3	FXIO0_D1	LCD_P56
11	7	5	E2	PTE18	ADC0_DP2/ ADC0_SE2	LCD_P57/ ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO	FXIO0_D2	LCD_P57
12	8	6	D2	PTE19	ADC0_DM2/ ADC0_SE6a	LCD_P58/ ADC0_DM2/ ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI	FXIO0_D3	LCD_P58
13	9	7	G1	PTE20	ADC0_DP0/ ADC0_SE0	LCD_P59/ ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	LPUART0_ TX		FXIO0_D4	LCD_P59
14	10	8	F1	PTE21	ADC0_DM0/ ADC0_SE4a	LCD_P60/ ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	LPUART0_ RX		FXIO0_D5	LCD_P60
15	11	—	G2	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX		FXIO0_D6	
16	12	—	F2	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX		FXIO0_D7	
17	13	9	F4	VDDA	VDDA	VDDA							
18	14	10	G4	VREFH	VREFH	VREFH							
18	14	10	G4	VREFO	VREFO (1.2V reference, bond to VREFH)	VREFH							
19	15	11	G3	VREFL	VREFL	VREFL							
20	16	12	F3	VSSA	VSSA	VSSA							
21	17	13	H1	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_ CLKIN0			
22	18	14	H2	PTE30	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_ CLKIN1	LPUART1_ TX	LPTMR0_ ALT1	

## Pinouts and Packaging

80 LQFP	64 LQFP	48 QFN	64 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
23	19	—	H3	PTE31	DISABLED		PTE31		TPM0_CH4				
24	20	15	H4	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
25	21	16	H5	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
26	22	17	D3	PTA0	SWD_CLK		PTA0		TPM0_CH5				SWD_CLK
27	23	18	D4	PTA1	DISABLED		PTA1	LPUART0_RX	TPM2_CH0				
28	24	19	E5	PTA2	DISABLED		PTA2	LPUART0_TX	TPM2_CH1				
29	25	20	D5	PTA3	SWD_DIO		PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
30	26	21	G5	PTA4	NMI_b		PTA4	I2C1_SDA	TPM0_CH1				NMI_b
31	27	—	F5	PTA5	DISABLED		PTA5		TPM0_CH2				
32	28	—	H6	PTA12	DISABLED		PTA12		TPM1_CH0				
33	29	—	G6	PTA13	DISABLED		PTA13		TPM1_CH1				
34	—	—	—	PTA14	DISABLED		PTA14	SPI0_PCS0	LPUART0_TX				
35	—	—	—	PTA15	DISABLED		PTA15	SPI0_SCK	LPUART0_RX				
36	—	—	—	PTA16	DISABLED		PTA16	SPI0_MOSI			SPI0_MISO		
37	—	—	—	PTA17	DISABLED		PTA17	SPI0_MISO			SPI0_MOSI		
38	30	22	G7	VDD	VDD	VDD							
39	31	23	H7	VSS	VSS	VSS							
40	32	24	H8	PTA18	EXTAL0	EXTAL0	PTA18		LPUART1_RX	TPM_CLKIN0			
41	33	25	G8	PTA19	XTAL0	XTAL0	PTA19		LPUART1_TX	TPM_CLKIN1		LPTMR0_ALT1	
42	34	26	F8	PTA20	RESET_b		PTA20						RESET_b
43	35	27	F7	PTB0/ LLWU_P5	LCD_P0/ ADC0_SE8	LCD_P0/ ADC0_SE8	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0	SPI1_MOSI	SPI1_MISO		LCD_P0
44	36	28	F6	PTB1	LCD_P1/ ADC0_SE9	LCD_P1/ ADC0_SE9	PTB1	I2C0_SDA	TPM1_CH1	SPI1_MISO	SPI1_MOSI		LCD_P1
45	37	29	E7	PTB2	LCD_P2/ ADC0_SE12	LCD_P2/ ADC0_SE12	PTB2	I2C0_SCL	TPM2_CH0				LCD_P2
46	38	30	E8	PTB3	LCD_P3/ ADC0_SE13	LCD_P3/ ADC0_SE13	PTB3	I2C0_SDA	TPM2_CH1				LCD_P3
47	—	—	—	PTB8	LCD_P8	LCD_P8	PTB8	SPI1_PCS0	EXTRG_IN				LCD_P8
48	—	—	—	PTB9	LCD_P9	LCD_P9	PTB9	SPI1_SCK					LCD_P9
49	—	—	—	PTB10	LCD_P10	LCD_P10	PTB10	SPI1_PCS0					LCD_P10
50	—	—	—	PTB11	LCD_P11	LCD_P11	PTB11	SPI1_SCK					LCD_P11
51	39	—	E6	PTB16	LCD_P12	LCD_P12	PTB16	SPI1_MOSI	LPUART0_RX	TPM_CLKIN0	SPI1_MISO		LCD_P12
52	40	—	D7	PTB17	LCD_P13	LCD_P13	PTB17	SPI1_MISO	LPUART0_TX	TPM_CLKIN1	SPI1_MOSI		LCD_P13

80 LQFP	64 LQFP	48 QFN	64 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
53	41	—	D6	PTB18	LCD_P14	LCD_P14	PTB18		TPM2_CH0				LCD_P14
54	42	—	C7	PTB19	LCD_P15	LCD_P15	PTB19		TPM2_CH1				LCD_P15
55	43	31	D8	PTC0	LCD_P20/ ADC0_SE14	LCD_P20/ ADC0_SE14	PTC0		EXTRG_IN		CMP0_OUT		LCD_P20
56	44	32	C6	PTC1/ LLWU_P6/ RTC_CLKIN	LCD_P21/ ADC0_SE15	LCD_P21/ ADC0_SE15	PTC1/ LLWU_P6/ RTC_CLKIN	I2C1_SCL		TPM0_CH0			LCD_P21
57	45	33	B7	PTC2	LCD_P22/ ADC0_SE11	LCD_P22/ ADC0_SE11	PTC2	I2C1_SDA		TPM0_CH1			LCD_P22
58	46	34	C8	PTC3/ LLWU_P7	LCD_P23	LCD_P23	PTC3/ LLWU_P7	SPI1_SCK	LPUART1_ RX	TPM0_CH2	CLKOUT		LCD_P23
59	47	35	E3	VSS	VSS	VSS							
60	48	36	C5	VLL3	VLL3	VLL3							
61	49	37	A6	VLL2	VLL2	VLL2/ LCD_P4	PTC20						LCD_P4
62	50	38	B5	VLL1	VLL1	VLL1/ LCD_P5	PTC21						LCD_P5
63	51	39	B4	VCAP2	VCAP2	VCAP2/ LCD_P6	PTC22						LCD_P6
64	52	40	A5	VCAP1	VCAP1	VCAP1/ LCD_P39	PTC23						LCD_P39
65	53	41	B8	PTC4/ LLWU_P8	LCD_P24	LCD_P24	PTC4/ LLWU_P8	SPI0_PCS0	LPUART1_ TX	TPM0_CH3	SPI1_PCS0		LCD_P24
66	54	42	A8	PTC5/ LLWU_P9	LCD_P25	LCD_P25	PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ ALT2			CMP0_OUT	LCD_P25
67	55	43	A7	PTC6/ LLWU_P10	LCD_P26/ CMP0_IN0	LCD_P26/ CMP0_IN0	PTC6/ LLWU_P10	SPI0_MOSI	EXTRG_IN		SPI0_MISO		LCD_P26
68	56	44	B6	PTC7	LCD_P27/ CMP0_IN1	LCD_P27/ CMP0_IN1	PTC7	SPI0_MISO			SPI0_MOSI		LCD_P27
69	—	—	—	PTC8	LCD_P28/ CMP0_IN2	LCD_P28/ CMP0_IN2	PTC8	I2C0_SCL	TPM0_CH4				LCD_P28
70	—	—	—	PTC9	LCD_P29/ CMP0_IN3	LCD_P29/ CMP0_IN3	PTC9	I2C0_SDA	TPM0_CH5				LCD_P29
71	—	—	—	PTC10	LCD_P30	LCD_P30	PTC10	I2C1_SCL					LCD_P30
72	—	—	—	PTC11	LCD_P31	LCD_P31	PTC11	I2C1_SDA					LCD_P31
73	57	—	C3	PTD0	LCD_P40	LCD_P40	PTD0	SPI0_PCS0		TPM0_CH0		FXIO0_D0	LCD_P40
74	58	—	A4	PTD1	LCD_P41/ ADC0_SE5b	LCD_P41/ ADC0_SE5b	PTD1	SPI0_SCK		TPM0_CH1		FXIO0_D1	LCD_P41
75	59	—	C2	PTD2	LCD_P42	LCD_P42	PTD2	SPI0_MOSI	UART2_RX	TPM0_CH2	SPI0_MISO	FXIO0_D2	LCD_P42
76	60	—	B3	PTD3	LCD_P43	LCD_P43	PTD3	SPI0_MISO	UART2_TX	TPM0_CH3	SPI0_MOSI	FXIO0_D3	LCD_P43
77	61	45	A3	PTD4/ LLWU_P14	LCD_P44	LCD_P44	PTD4/ LLWU_P14	SPI1_PCS0	UART2_RX	TPM0_CH4		FXIO0_D4	LCD_P44
78	62	46	C1	PTD5	LCD_P45/ ADC0_SE6b	LCD_P45/ ADC0_SE6b	PTD5	SPI1_SCK	UART2_TX	TPM0_CH5		FXIO0_D5	LCD_P45

## Pinouts and Packaging

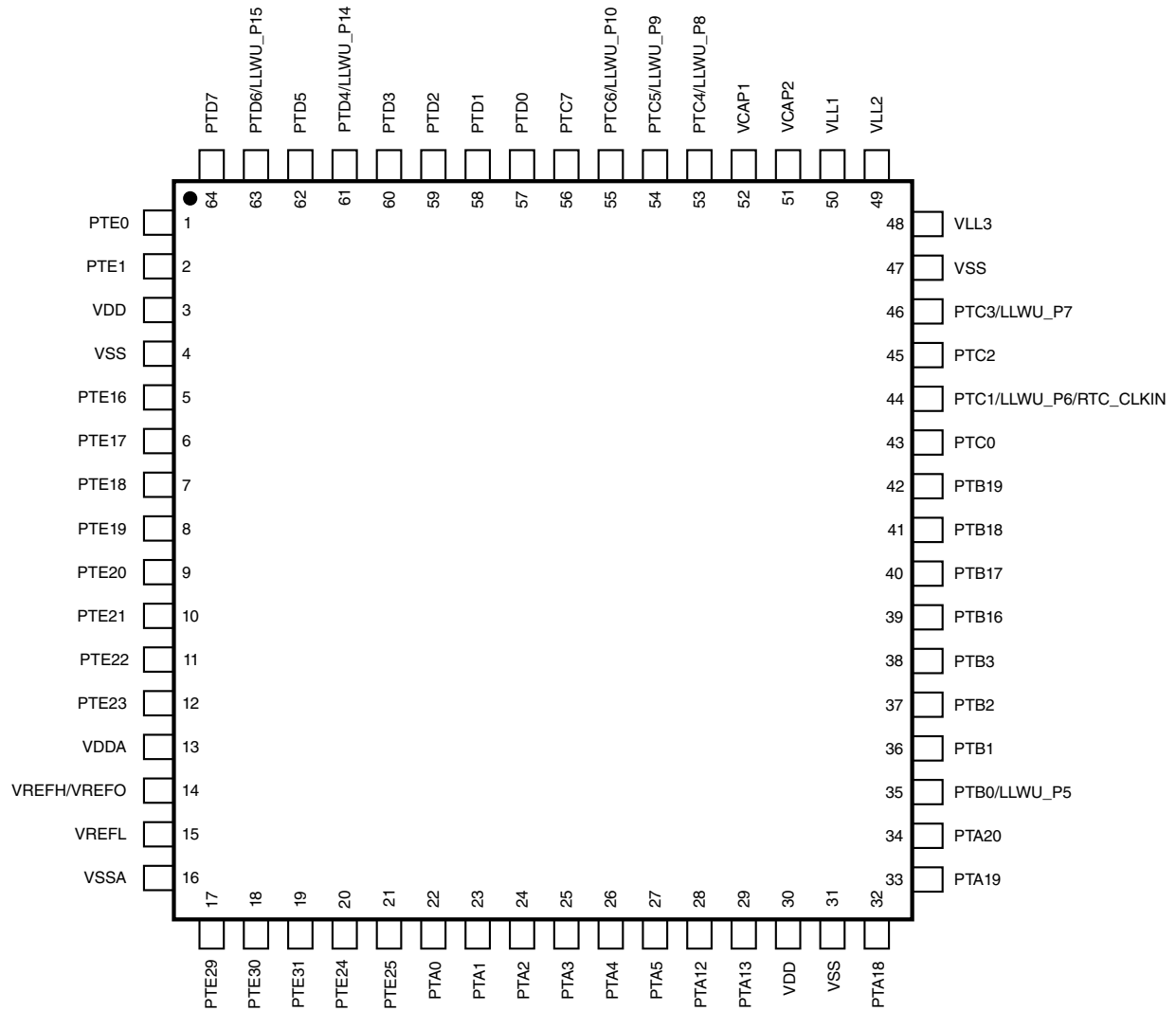
80 LQFP	64 LQFP	48 QFN	64 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
79	63	47	B2	PTD6/ LLWU_P15	LCD_P46/ ADC0_SE7b	LCD_P46/ ADC0_SE7b	PTD6/ LLWU_P15	SPI1_MOSI	LPUART0_ RX	I2C1_SDA	SPI1_MISO	FXIO0_D6	LCD_P46
80	64	48	A2	PTD7	LCD_P47	LCD_P47	PTD7	SPI1_MISO	LPUART0_ TX	I2C1_SCL	SPI1_MOSI	FXIO0_D7	LCD_P47

## 9.2 KL33 Family Pinouts

Figure below shows the 64 LQFP pinouts:

### NOTE

The 48 QFN and 64 MAPBGA packages for this product are not yet available. However, these packages are included in Package Your Way program for Kinetis MCUs. Visit [freescale.com/KPYW](http://freescale.com/KPYW) for more details.



**Figure 28. 64 LQFP Pinout diagram**

Figure below shows the 80 LQFP pinouts:

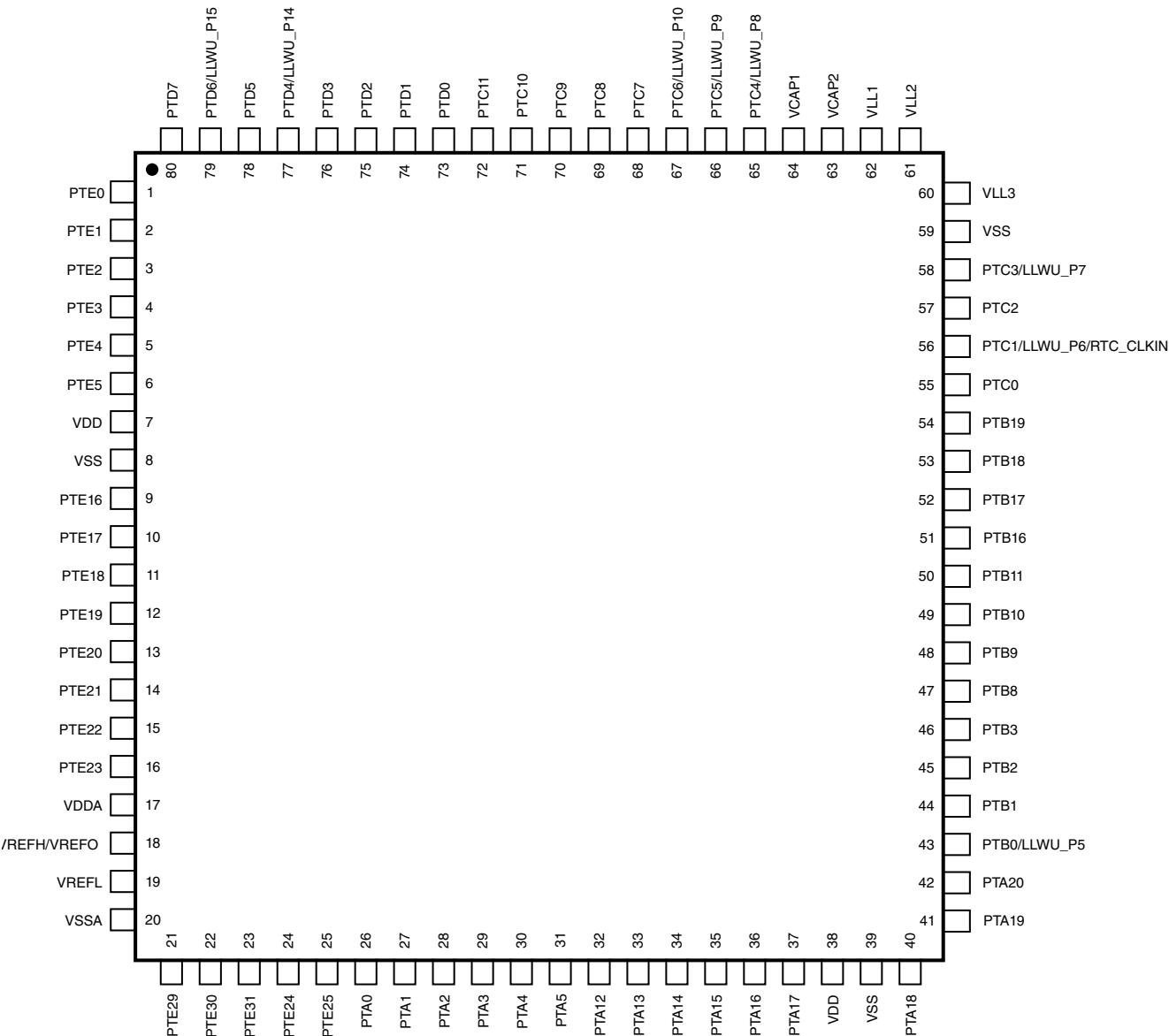


Figure 29. 80 LQFP Pinout diagram

Figure below shows the 64 MAPBGA pinouts:

	1	2	3	4	5	6	7	8	
A	PTE0	PTD7	PTD4/ LLWU_P14	PTD1	VCAP1	VLL2	PTC6/ LLWU_P10	PTC5/ LLWU_P9	A
B	PTE1	PTD6/ LLWU_P15	PTD3	VCAP2	VLL1	PTC7	PTC2	PTC4/ LLWU_P8	B
C	PTD5	PTD2	PTD0	VSS	VLL3	PTC1/ LLWU_P6/ RTC_CLKIN	PTB19	PTC3/ LLWU_P7	C
D	PTE17	PTE19	PTA0	PTA1	PTA3	PTB18	PTB17	PTC0	D
E	PTE16	PTE18	VSS	VDD	PTA2	PTB16	PTB2	PTB3	E
F	PTE21	PTE23	VSSA	VDDA	PTA5	PTB1	PTB0/ LLWU_P5	PTA20	F
G	PTE20	PTE22	VREFL	VREFH/ VREFO	PTA4	PTA13	VDD	PTA19	G
H	PTE29	PTE30	PTE31	PTE24	PTE25	PTA12	VSS	PTA18	H
	1	2	3	4	5	6	7	8	

**Figure 30. 64 MAPBGA Pinout diagram**

Figure below shows the 48 QFN pinouts:

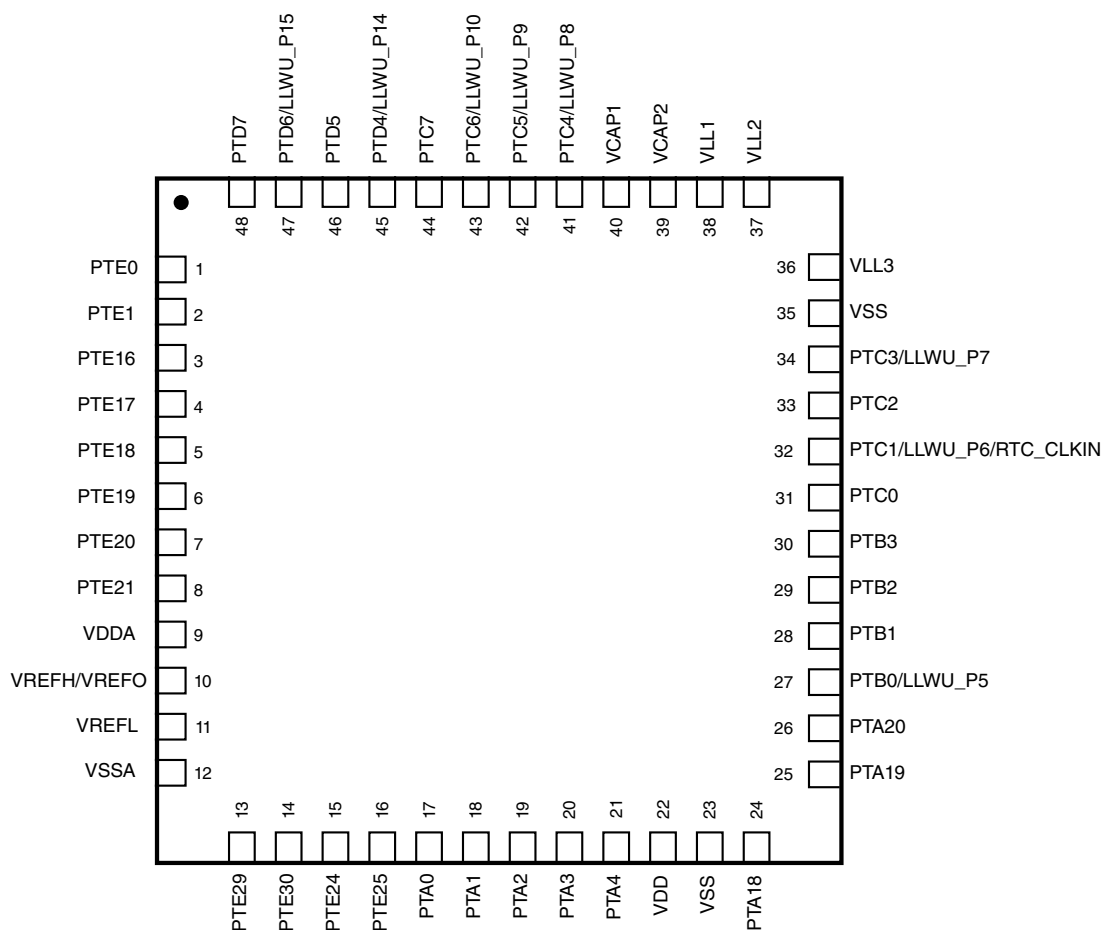


Figure 31. 48 QFN Pinout diagram

## 10 Ordering parts

### 10.1 Determining valid orderable parts

Valid orderable part numbers are provided on the Web. To determine the orderable part numbers for this device, go to [freescale.com](http://freescale.com) and perform a part number search for the following device numbers:

## 11 Part identification



## 11.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

## 11.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

## 11.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

**Table 42. Part number fields description**

Field	Description	Values
Q	Qualification status	<ul style="list-style-type: none"> <li>M = Fully qualified, general market flow</li> <li>P = Prequalification</li> </ul>
KL##	Kinetis family	<ul style="list-style-type: none"> <li>KL33</li> </ul>
A	Key attribute	<ul style="list-style-type: none"> <li>Z = Cortex-M0+</li> </ul>
FFF	Program flash memory size	<ul style="list-style-type: none"> <li>32 = 32 KB</li> <li>64 = 64 KB</li> </ul>
R	Silicon revision	<ul style="list-style-type: none"> <li>(Blank) = Main</li> <li>A = Revision after main</li> </ul>
T	Temperature range (°C)	<ul style="list-style-type: none"> <li>V = -40 to 105</li> </ul>
PP	Package identifier	<ul style="list-style-type: none"> <li>FT = 48 QFN (7 mm x 7 mm)<sup>1</sup></li> <li>LH = 64 LQFP (10 mm x 10 mm)</li> <li>MP = 64 MAPBGA (5 mm x 5 mm)<sup>1</sup></li> <li>LK = 80 LQFP (12 mm x 12 mm)</li> </ul>
CC	Maximum CPU frequency (MHz)	<ul style="list-style-type: none"> <li>4 = 48 MHz</li> </ul>
N	Packaging type	<ul style="list-style-type: none"> <li>R = Tape and reel</li> </ul>

1. This package for this product is not yet available. However, it is included in Package Your Way program for Kinetis MCUs. Visit [freescale.com/KPYW](http://freescale.com/KPYW) for more details.

## 11.4 Example

This is an example part number:

MKL33Z32VLH4

## 12 Terminology and guidelines

### 12.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

#### 12.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V <sub>DD</sub>	1.0 V core supply voltage	0.9	1.1	V

### 12.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

#### 12.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I <sub>WP</sub>	Digital I/O weak pullup/pulldown current	10	130	μA

## 12.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

### 12.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

## 12.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

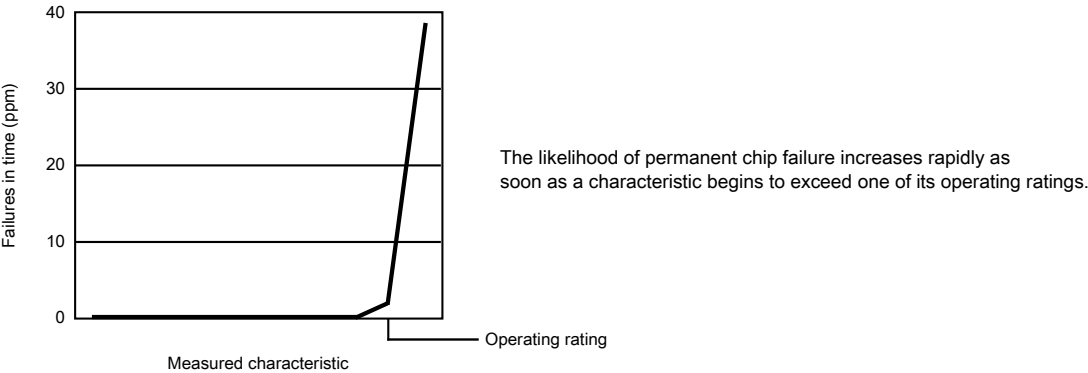
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

### 12.4.1 Example

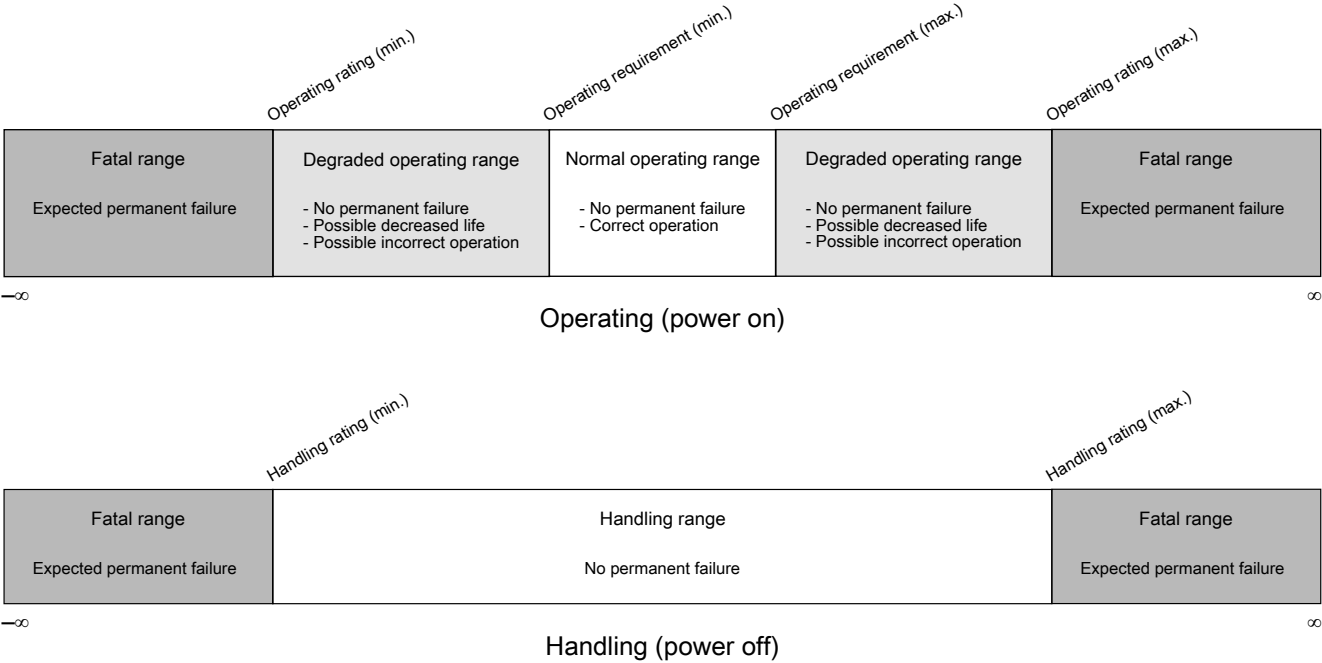
This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V <sub>DD</sub>	1.0 V core supply voltage	−0.3	1.2	V

12.5 Result of exceeding a rating



12.6 Relationship between ratings and operating requirements



12.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip’s ratings.
- During normal operation, don’t exceed any of the chip’s operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

## 12.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

### 12.8.1 Example 1

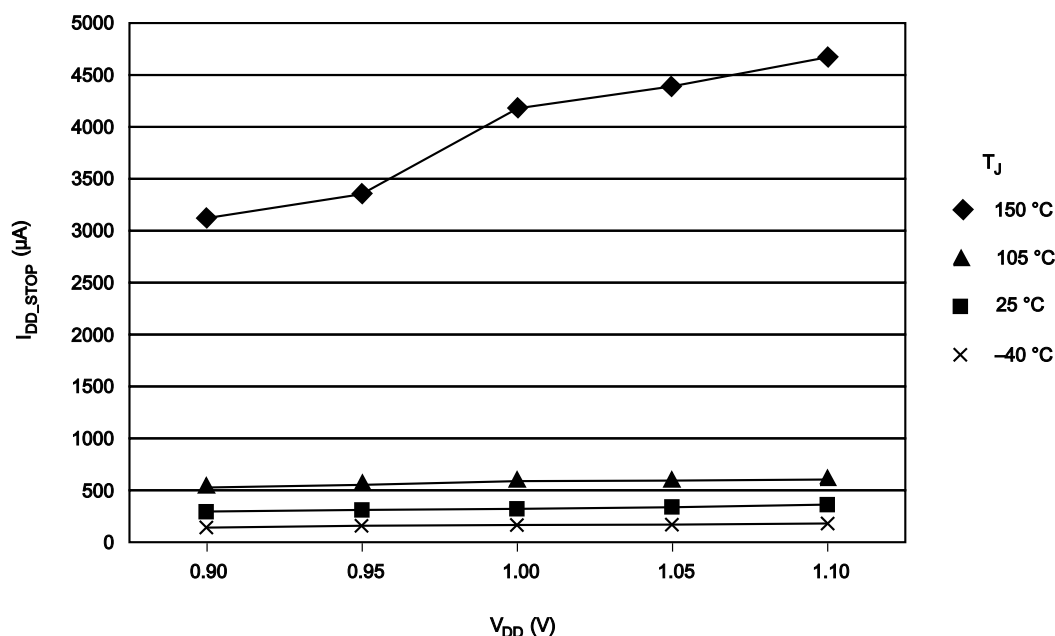
This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
$I_{WP}$	Digital I/O weak pullup/pulldown current	10	70	130	$\mu A$

### 12.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:

## Revision History



## 12.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

**Table 43. Typical value conditions**

Symbol	Description	Value	Unit
T <sub>A</sub>	Ambient temperature	25	°C
V <sub>DD</sub>	3.3 V supply voltage	3.3	V

## 13 Revision History

The following table provides a revision history for this document.

**Table 44. Revision History**

Rev. No.	Date	Substantial Changes
1	01 February 2015	<ul style="list-style-type: none"> <li>Added new topic "Electrical Design Considerations" as Section 6.</li> <li>Added a note in Table 14 - Thermal operating requirements.</li> <li>Footnote 1 in Table 9 was moved in the beginning of the table as text.</li> </ul>

*Table continues on the next page...*

**Table 44. Revision History (continued)**

Rev. No.	Date	Substantial Changes
2	18 March 2015	<ul style="list-style-type: none"> <li>Updated the features and completed the ordering information.</li> <li>Removed thickness dimension from package diagrams.</li> <li>Updated Table 7. Voltage and current operating behaviors. <ul style="list-style-type: none"> <li>Specified correct max. value for <math>I_{IN}</math> parameter.</li> </ul> </li> <li>Updated Table 8. Power mode transition operating behaviors with Typ. and Max. values.</li> <li>Updated Table 9. Power consumption operating behaviors with Typ. and Max. values.</li> <li>Updated Table 10. Low power mode peripheral adders — typical value.</li> <li>Updated EMC Performance information in section 2.2.6.</li> <li>Updated Table 17. IRC48M specification and Table 18. IRC8M/2M specification.</li> <li>Updated Typ. values of TUE and INL parameters in Table 26. 16-bit ADC characteristics.</li> <li>Updated Table 28. VREF full-range operating behaviors. <ul style="list-style-type: none"> <li>Removed <math>A_c</math>(Aging coefficient) row.</li> <li>Added <math>T_{chop\_osc\_stup}</math> parameter.</li> <li>Updated typical value of the <math>V_{out}</math> parameter.</li> </ul> </li> <li>Added tables: "I2C timing" and "I2C 1Mbit/s timing" under section - I2C.</li> <li>Updated Section 6 - Design Considerations.</li> </ul>



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